



Results From a Prototype TES Detector for the Ricochet Experiment

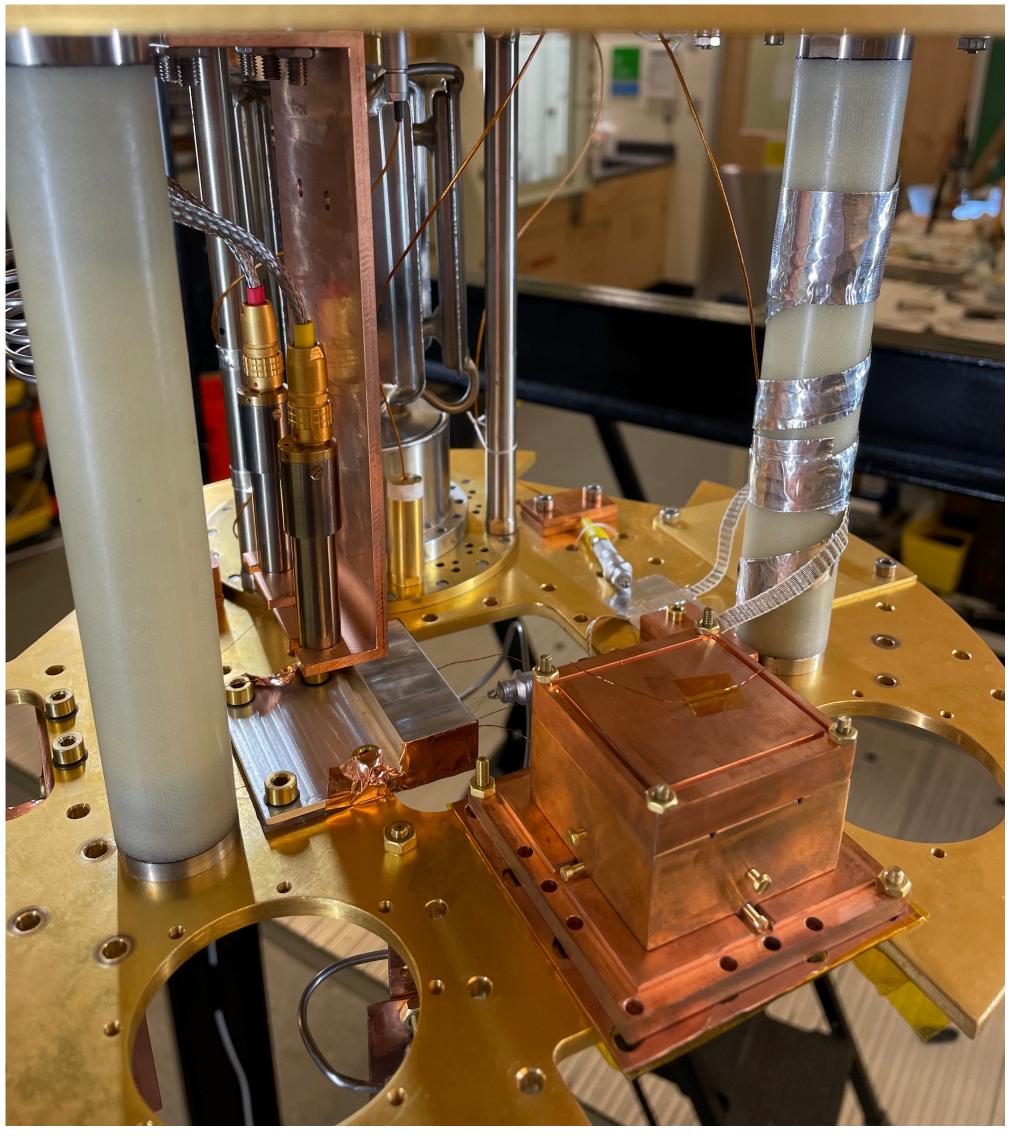
Doug Pinckney, on behalf of the Ricochet Collaboration 23 March 2023



Overview



- The Q-Array and TES detectors
- R&D from a proof-of-concept detector at UMass Amherst
- Future plans and conclusions

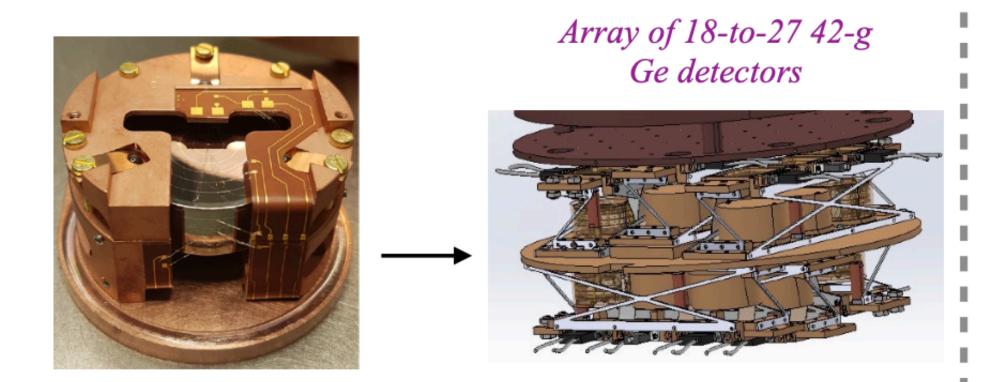


The Q-Array In Context Received Scattering Program

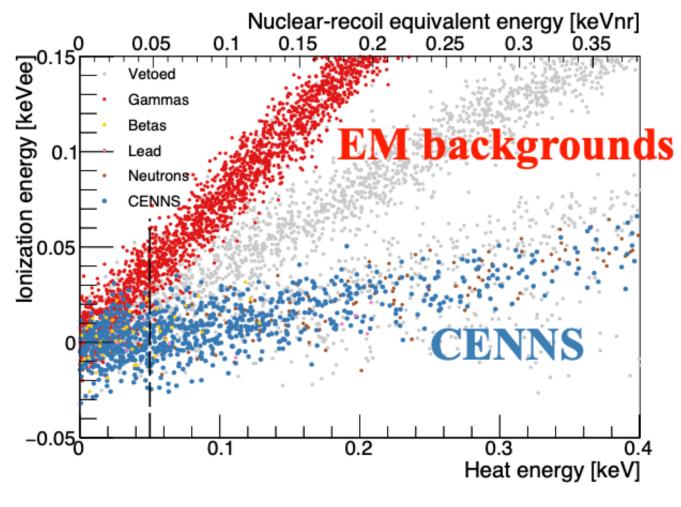


Technological key features of RICOCHET: Particle Identification down to sub-100 eV

Germanium semiconductor

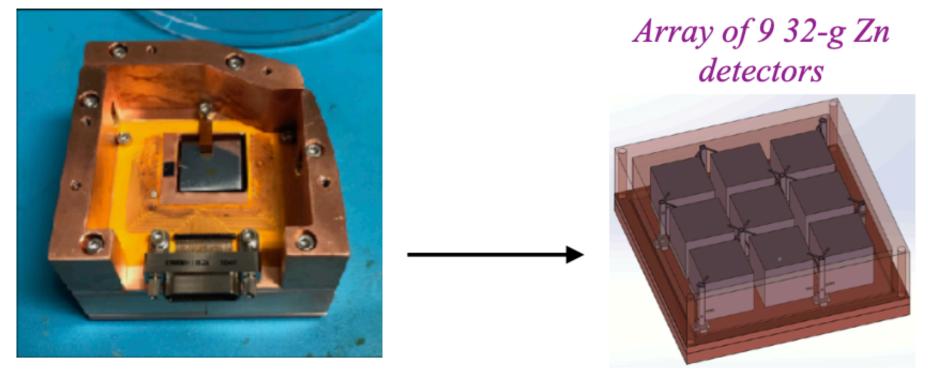


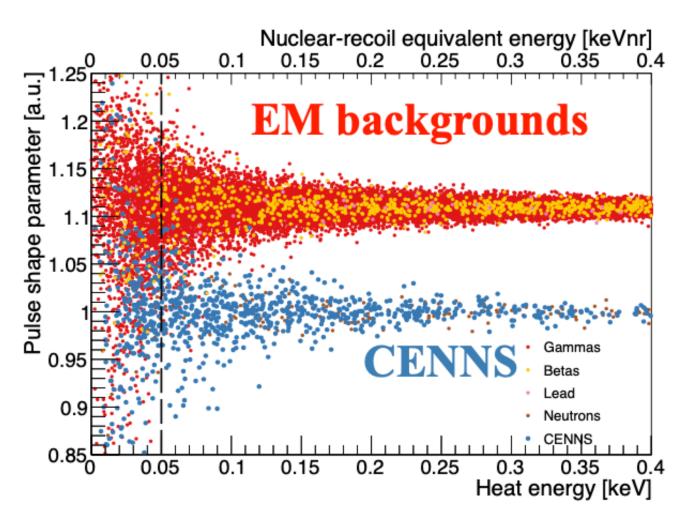
Slide from Julien Billard



Particle ID based on **Ionization / heat** ratio

Zinc superconducting metal





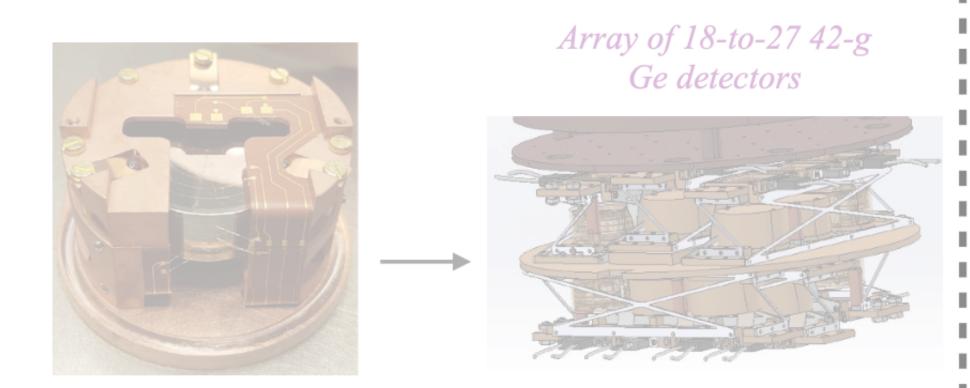
Particle ID based on **Prompt / delayed** heat signals

The Q-Array In Context RICO Scattering Program

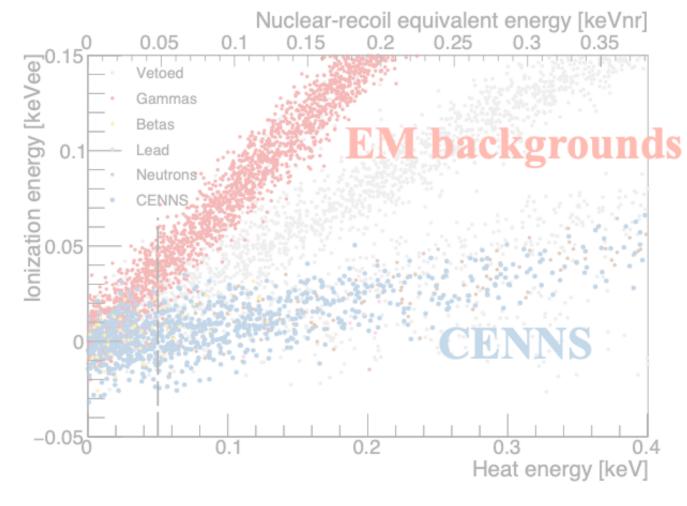


Technological key features of RICOCHET: Particle Identification down to sub-100 eV

Germanium semiconductor

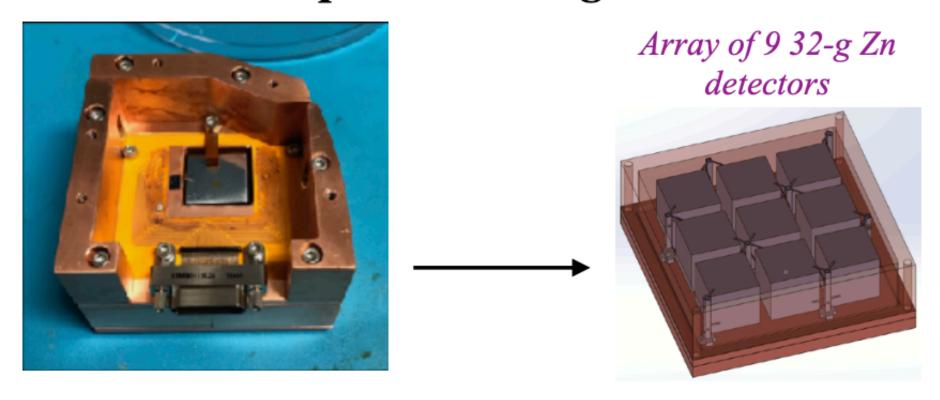


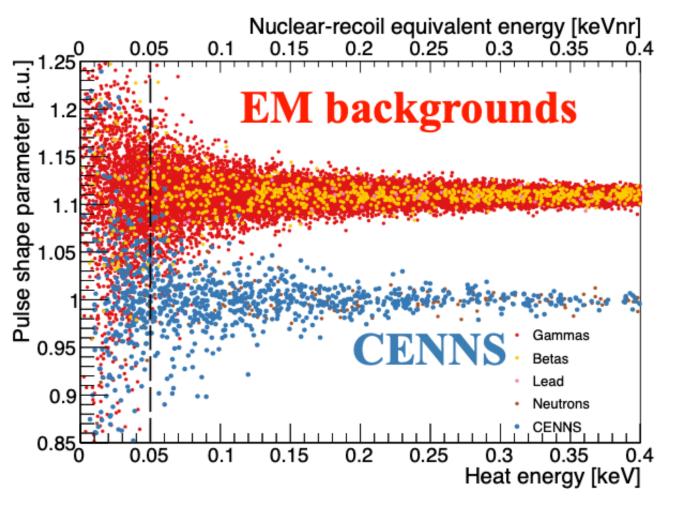
Slide from Julien Billard



Particle ID based on **Ionization / heat** ratio

Zinc superconducting metal



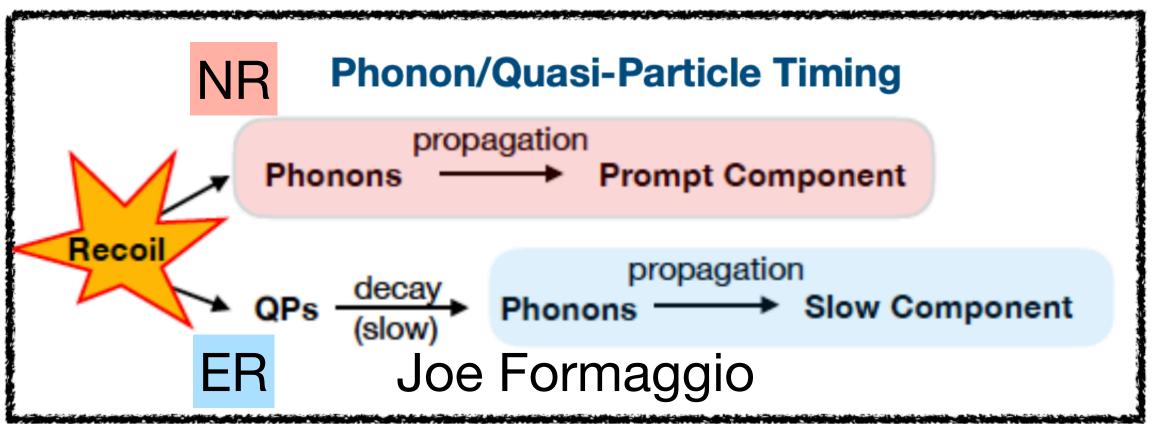


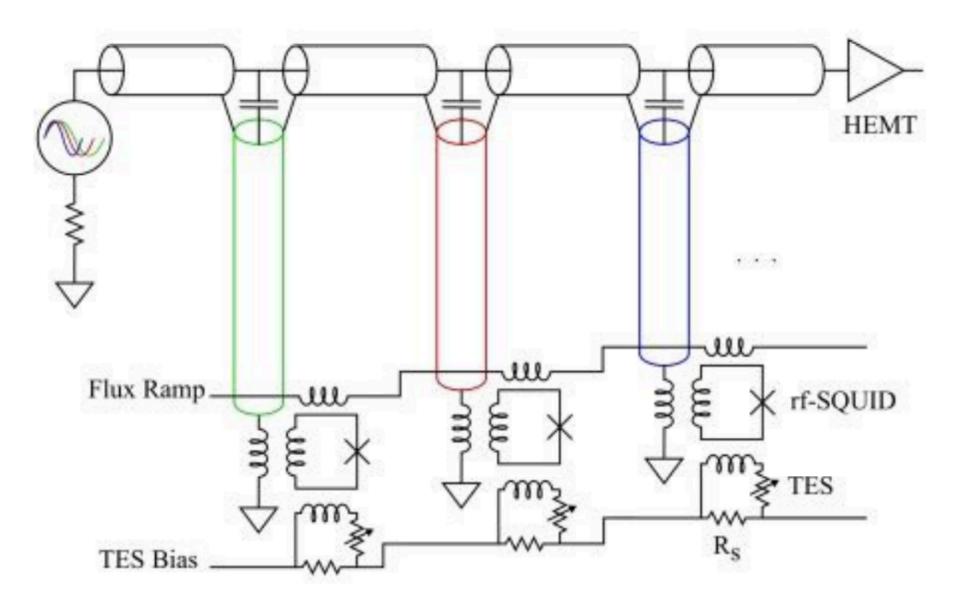
Particle ID based on **Prompt / delayed** heat signals

The Q-Array

- TESs reading out superconducting targets (Al, Zn, Sn...)
- Particle identification through QP/phonon ratio
 - Different signal timing
- Multiplexed readout using RF SQUIDs
- TESs physically separated from the superconducting target allows for scalability



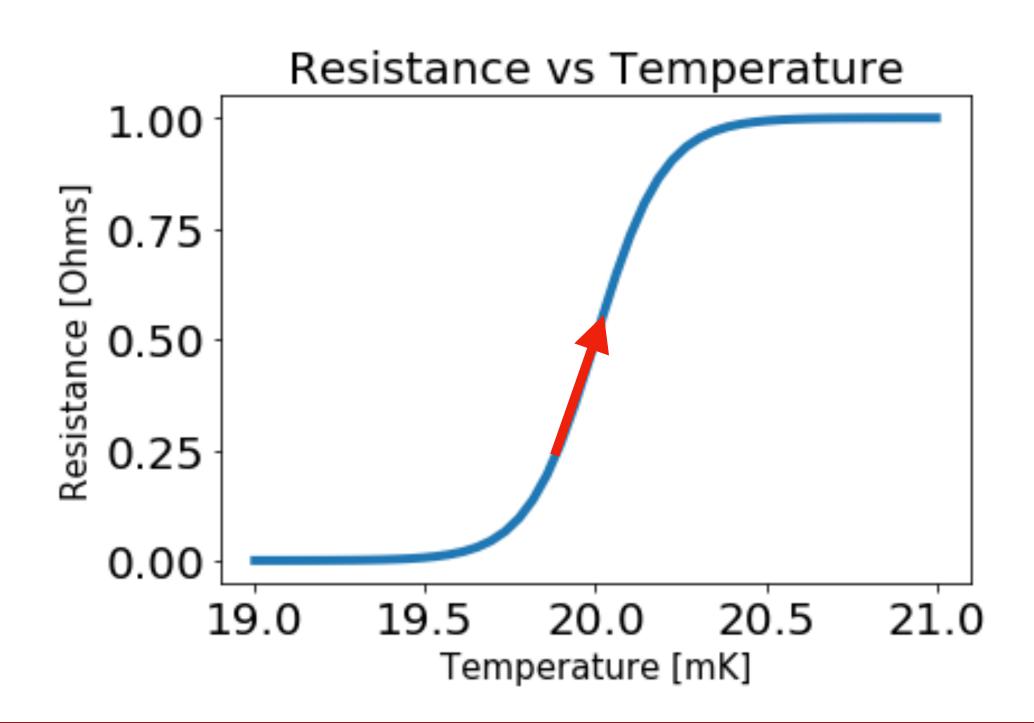


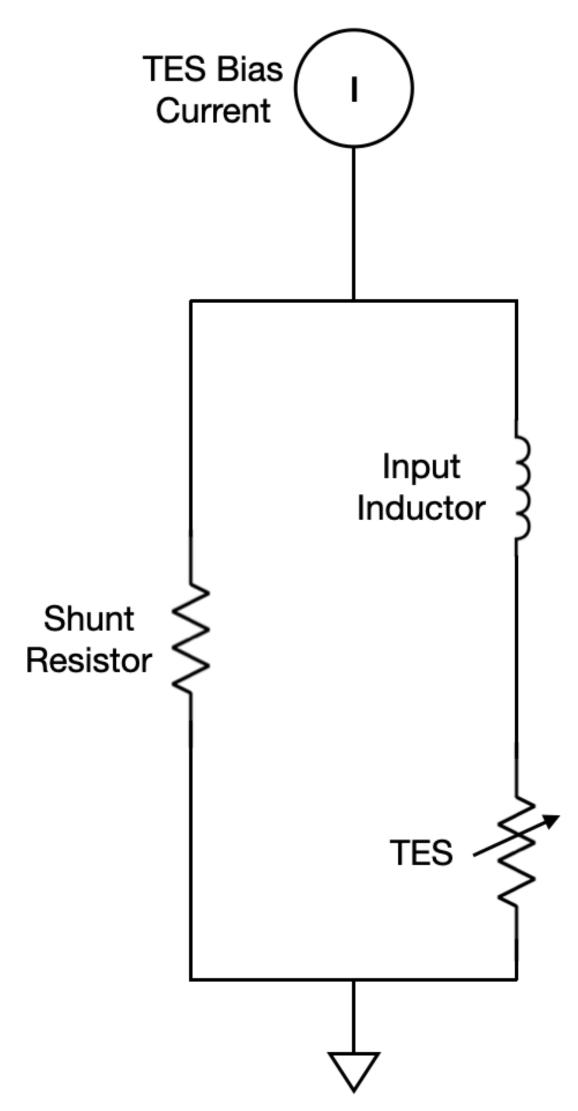


Simons Observatory

TESs and their Readout Richard Scattering Program

- In our application, a transition edge sensor (TES) converts temperature to current
- In general, the colder the TES the more sensitive it is (decreasing heat capacity)

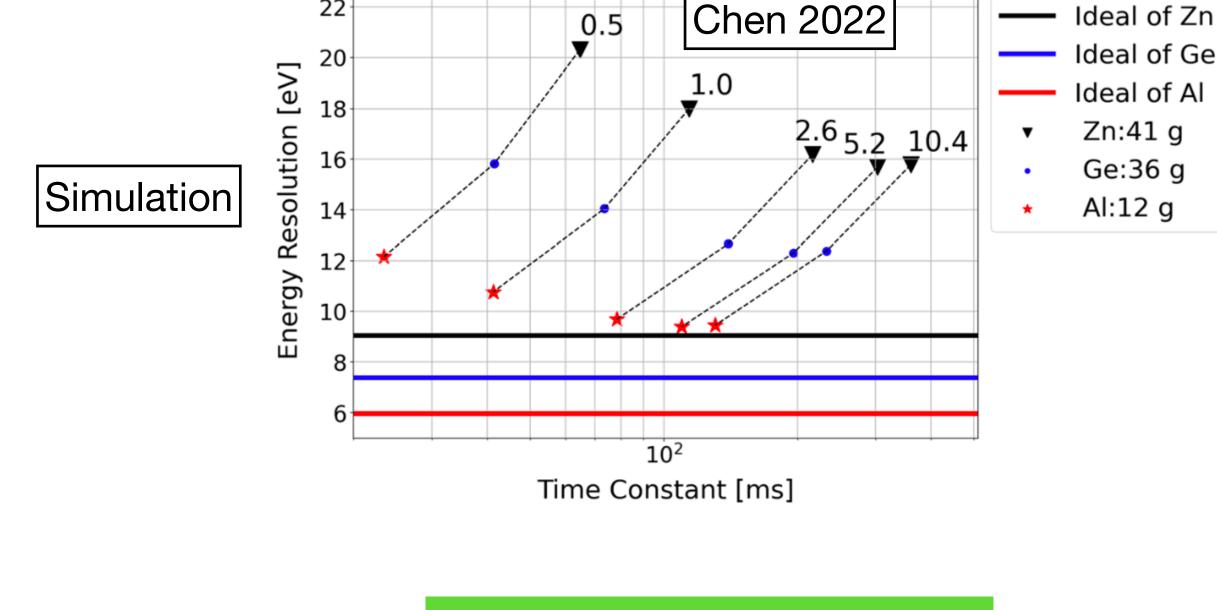


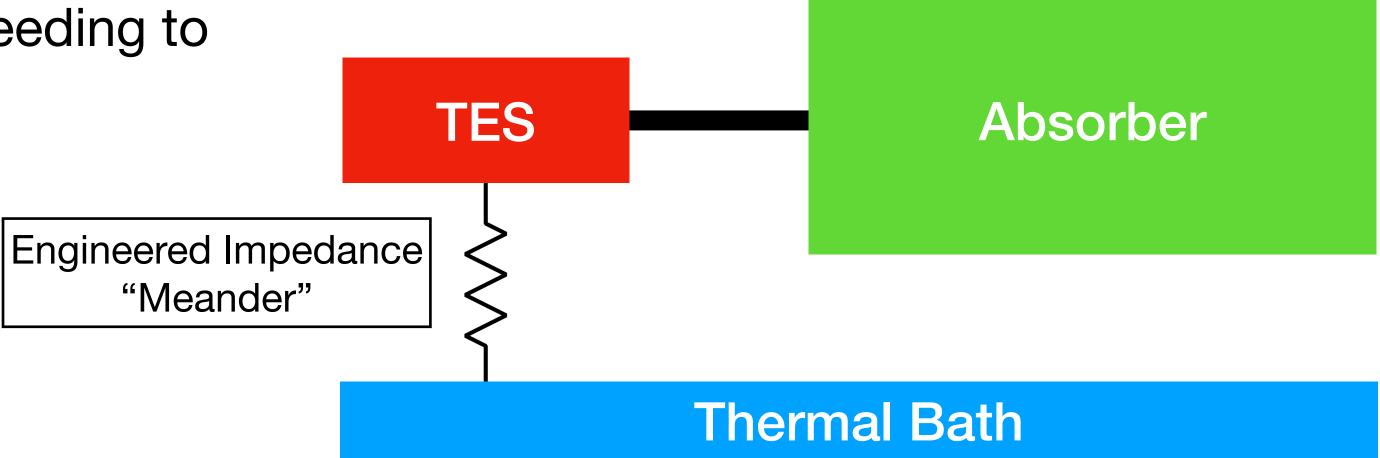


The Q-Array: TES Architecture

Ideal of Zn

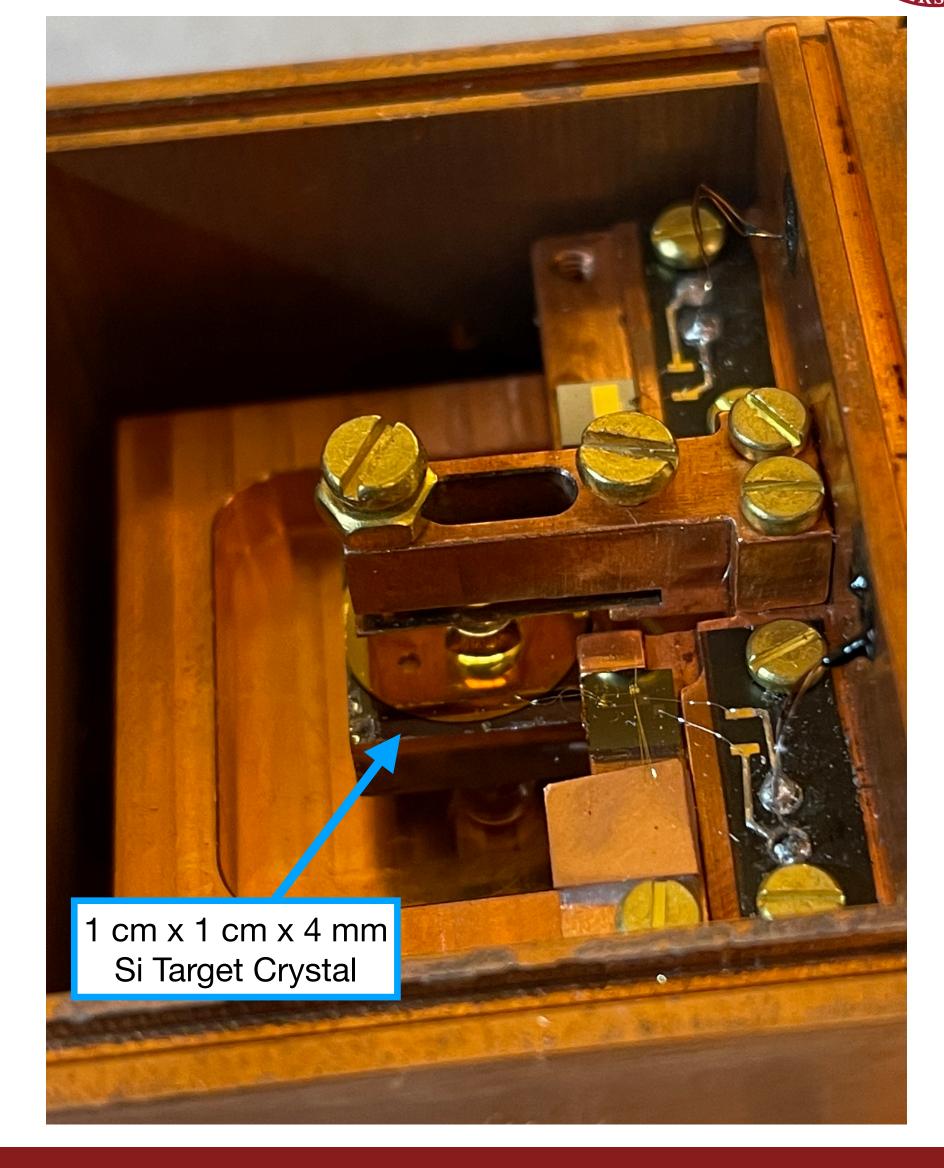
- Separate the TES from the target:
 - Fabricate many TESs at once
 - Allow for more target materials (superconductors, hygroscopic crystals)
- Angloher 2023, Chen 2022, Bastidon 2018
- Takes a penalty in efficiency, needing to transfer energy to the TES



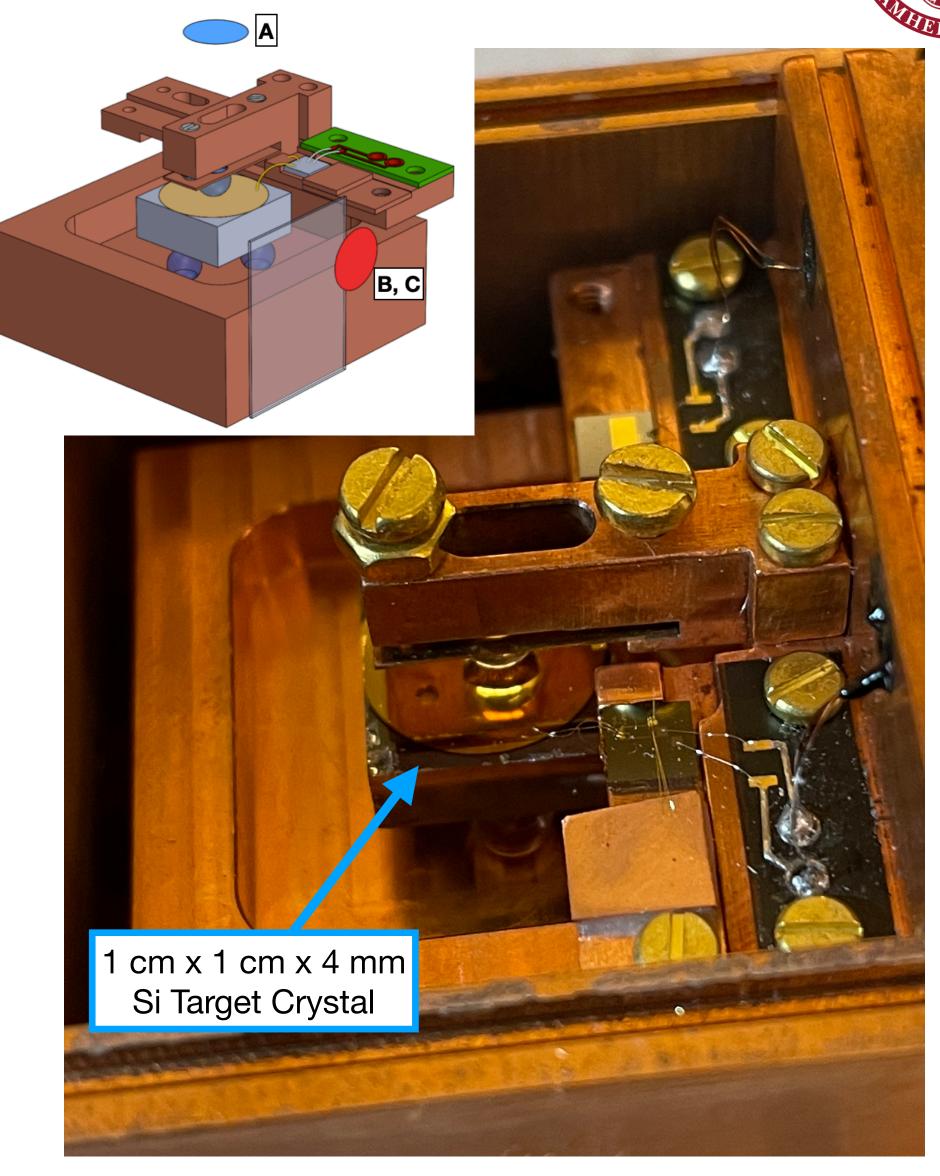




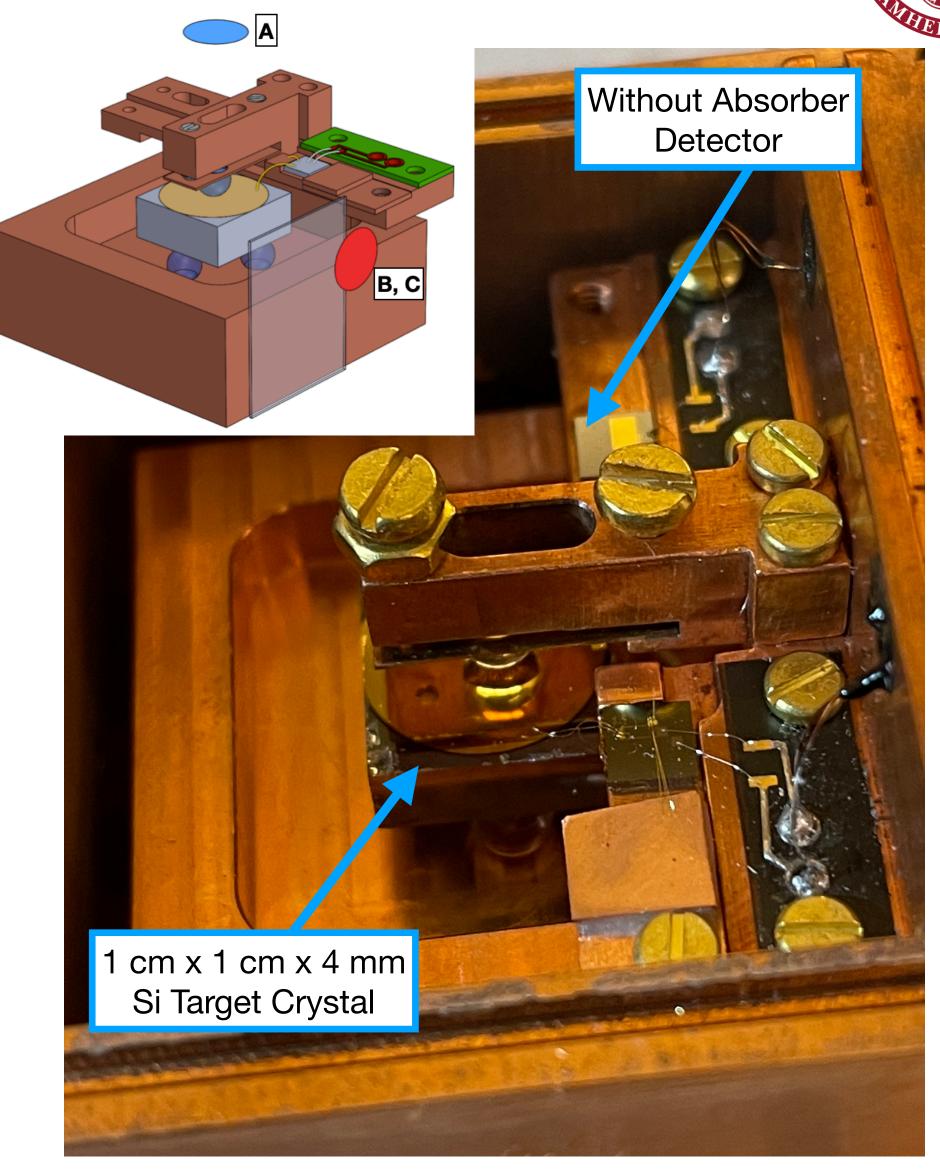
- Goal: Focus on understanding the TES and target material interface:
 - Small (1 g), non-superconducting crystal (Si) readout with DC SQUIDs



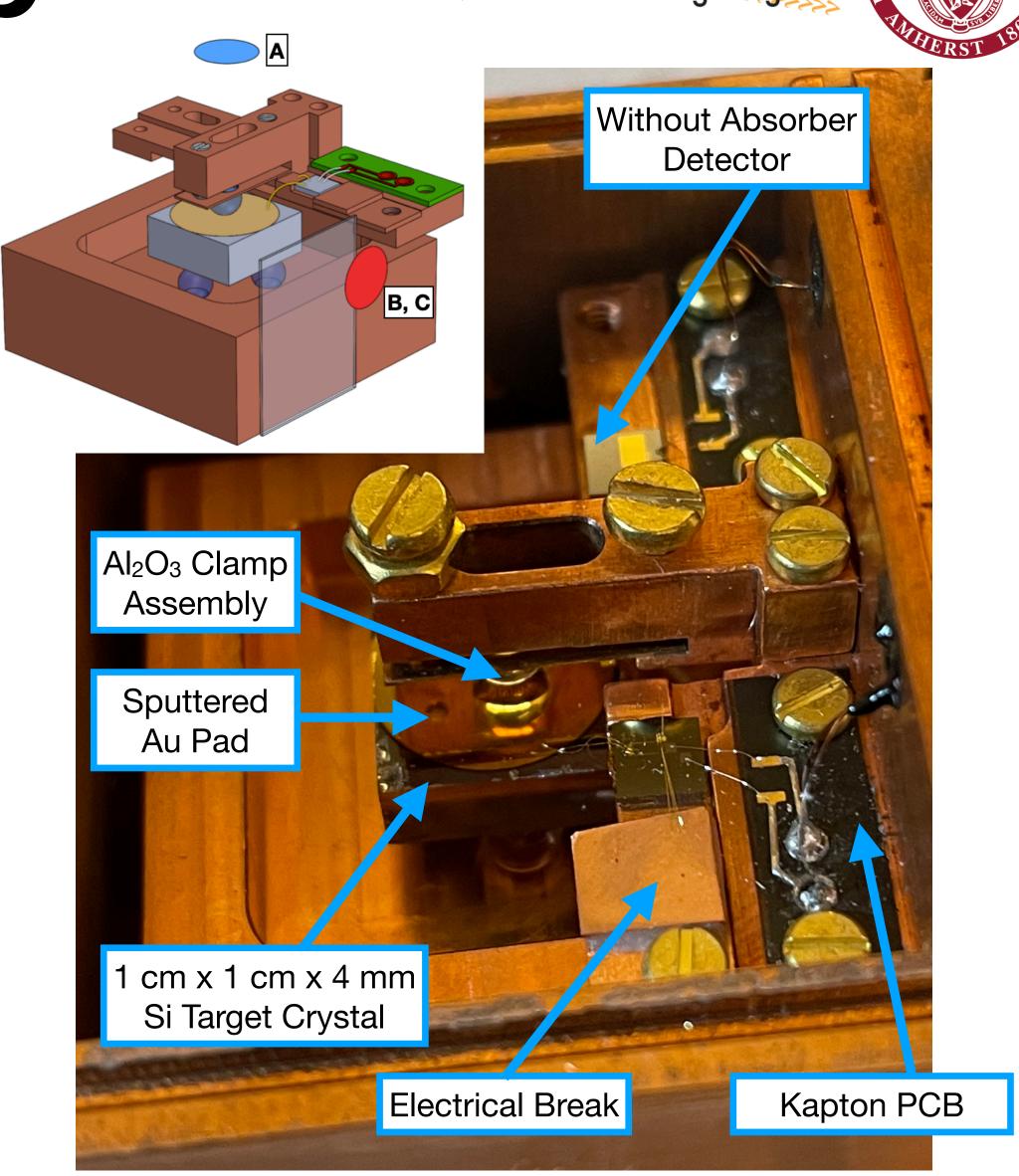
- Goal: Focus on understanding the TES and target material interface:
 - Small (1 g), non-superconducting crystal (Si) readout with DC SQUIDs
- Flexible R&D holder design (accommodates a variety of targets)
- Use ⁵⁵Fe X-rays to calibrate. Runs with source in 3 locations: "A, B, C"



- Goal: Focus on understanding the TES and target material interface:
 - Small (1 g), non-superconducting crystal (Si) readout with DC SQUIDs
- Flexible R&D holder design (accommodates a variety of targets)
- Use ⁵⁵Fe X-rays to calibrate. Runs with source in 3 locations: "A, B, C"
- Two detectors: "with absorber" and "without absorber"

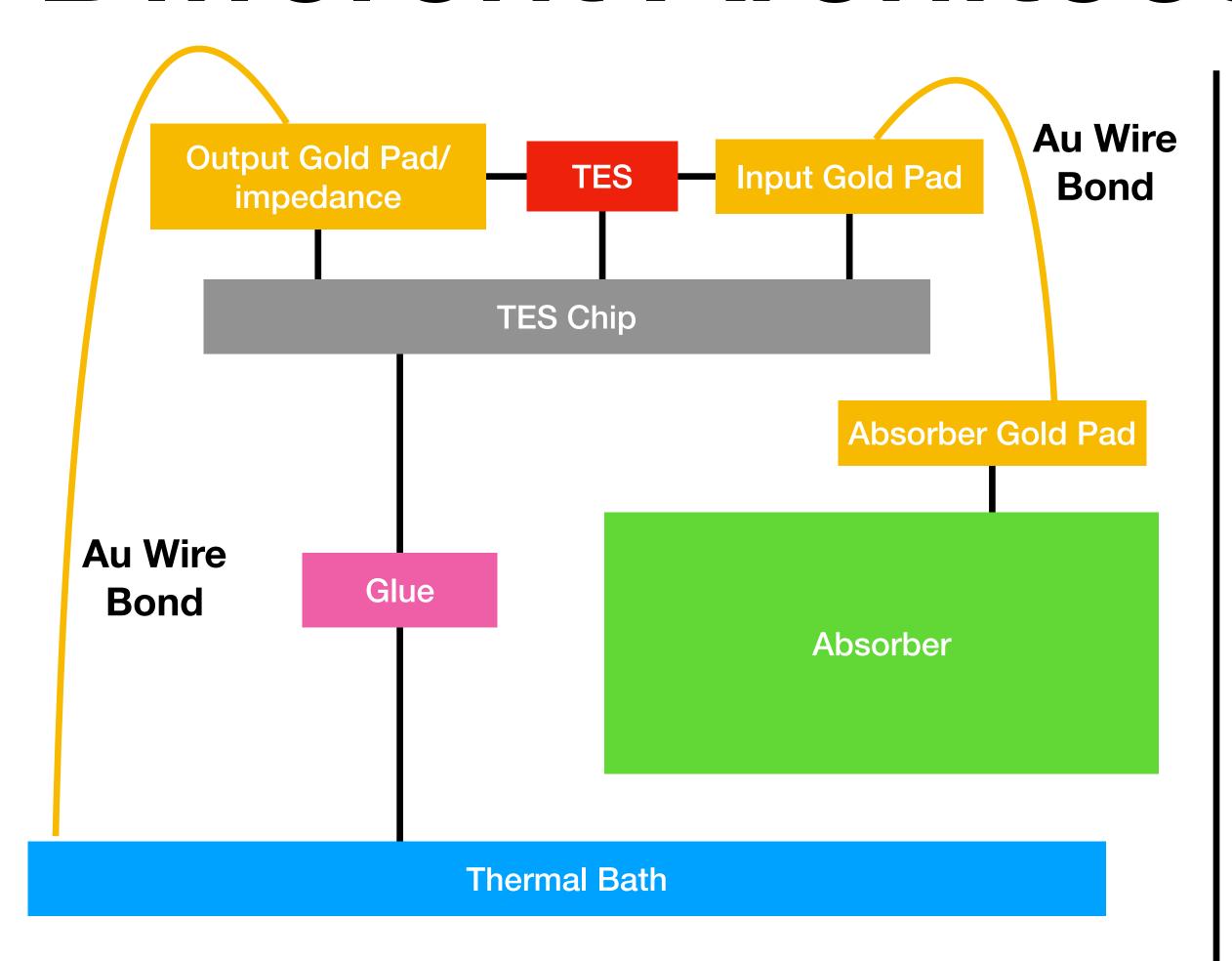


- Goal: Focus on understanding the TES and target material interface:
 - Small (1 g), non-superconducting crystal (Si) readout with DC SQUIDs
- Flexible R&D holder design (accommodates a variety of targets)
- Use ⁵⁵Fe X-rays to calibrate. Runs with source in 3 locations: "A, B, C"
- Two detectors: "with absorber" and "without absorber"



Different Architectures





Input Gold Pad TES Chip Thermal Bath

With Absorber

Without Absorber

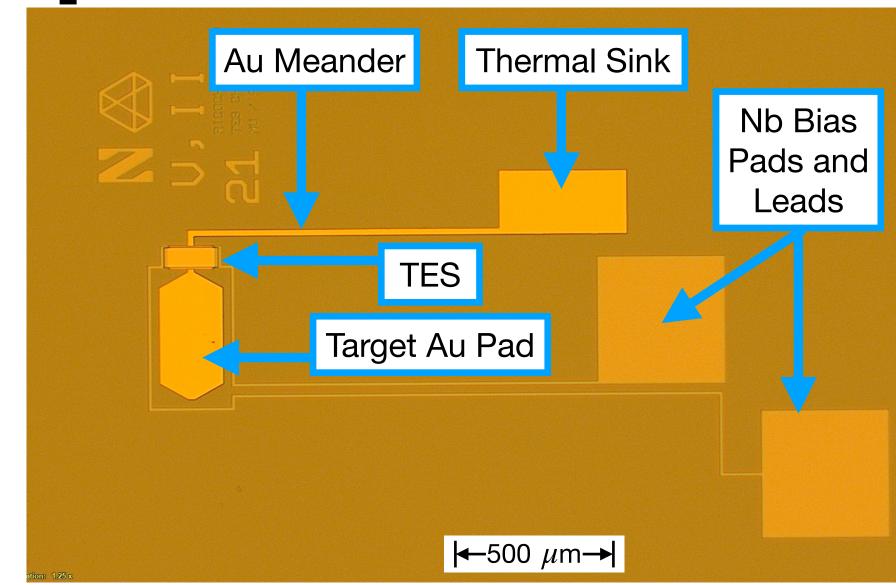
The Prototype Setup: TESs

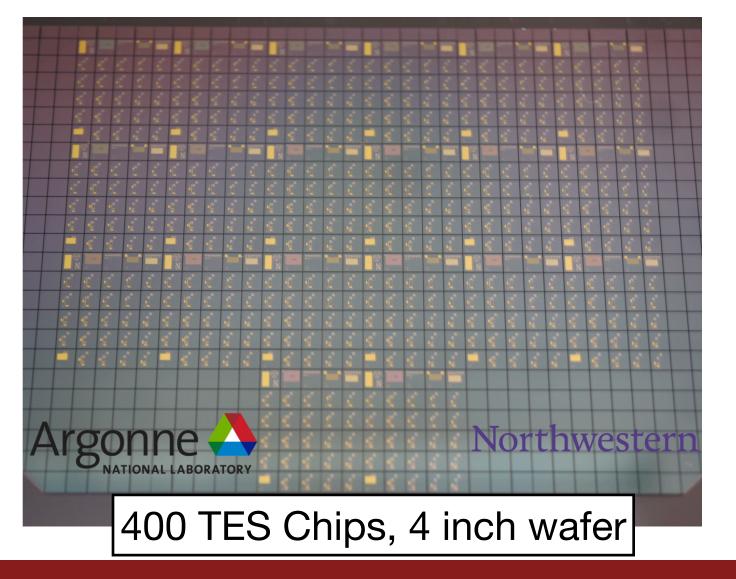
OF MASSACIAN WSETTS

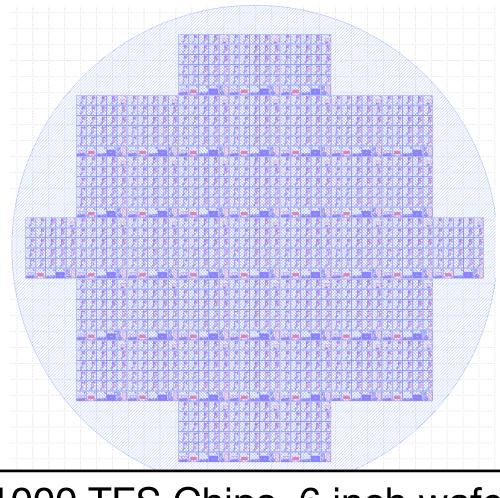
RESERVED TO SECTION OF THE REST TO SECTION OF T

- TESs fabricated at Argonne National Laboratory
 - AlMn films, bilayers with different levels of the Mn dopant
- Tc of "with absorber" detector approximately 20 mK
- Tc of "without absorber" detector was raised to ~40 mK through post-deposition heating







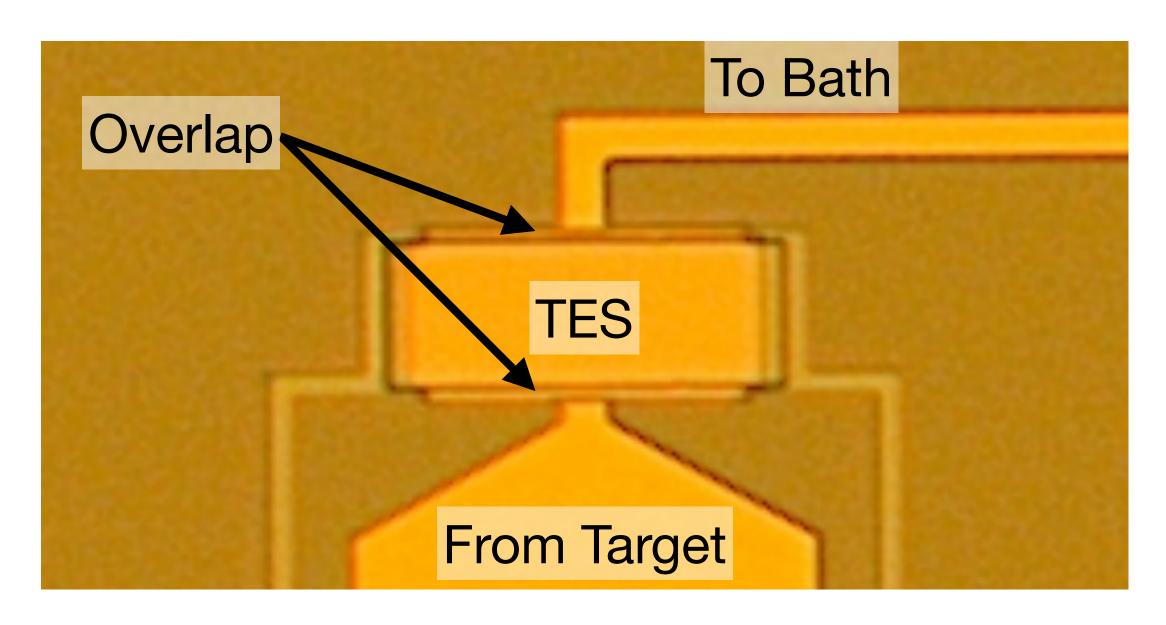


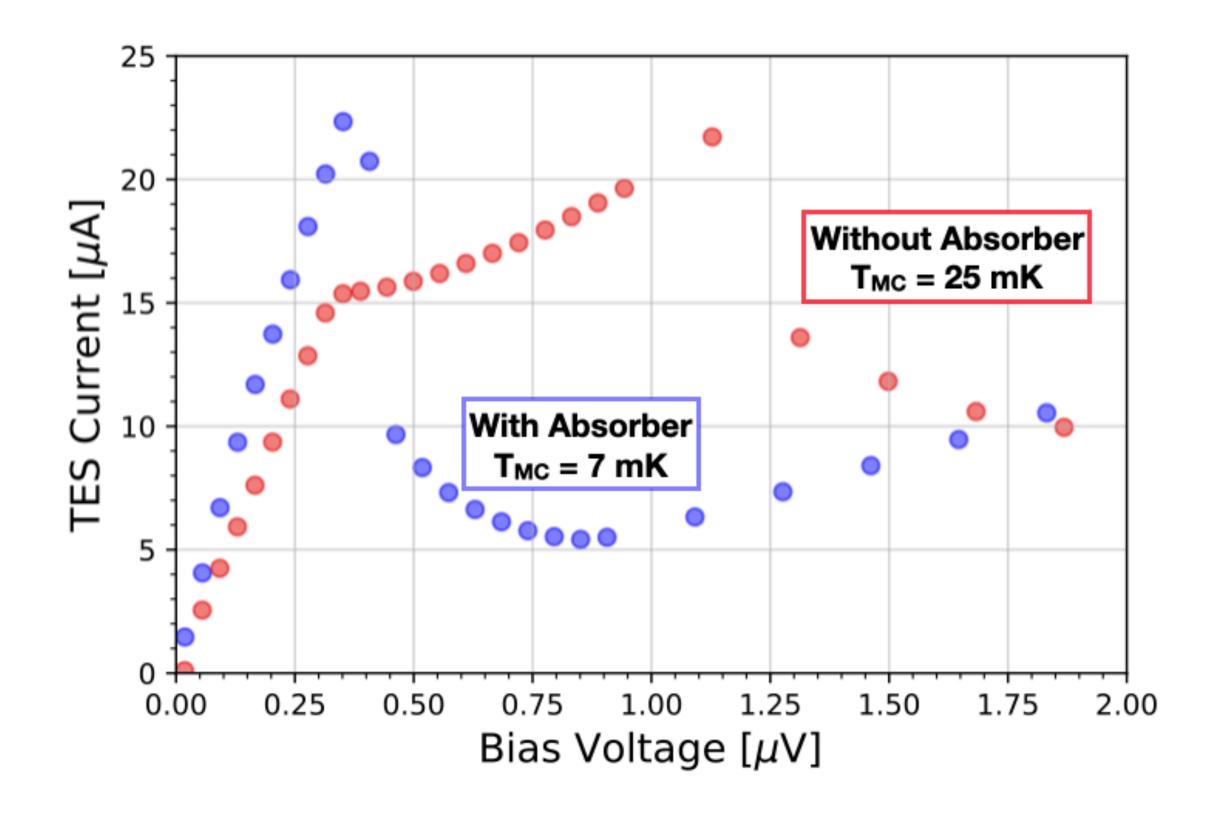
1000 TES Chips, 6 inch wafer

TES Performance



- Two transition features in each curve
 - Proximity effects from gold/TES overlap?





TES Channel	${\rm Rn} \ [{\rm m}\Omega]$	Tc [mK]	Bias Power [pW]
With Absorber Without Absorber	160 ± 20	20 ± 2	3.3 ± 0.3
	220 ± 20	38 ± 4	15 ± 2

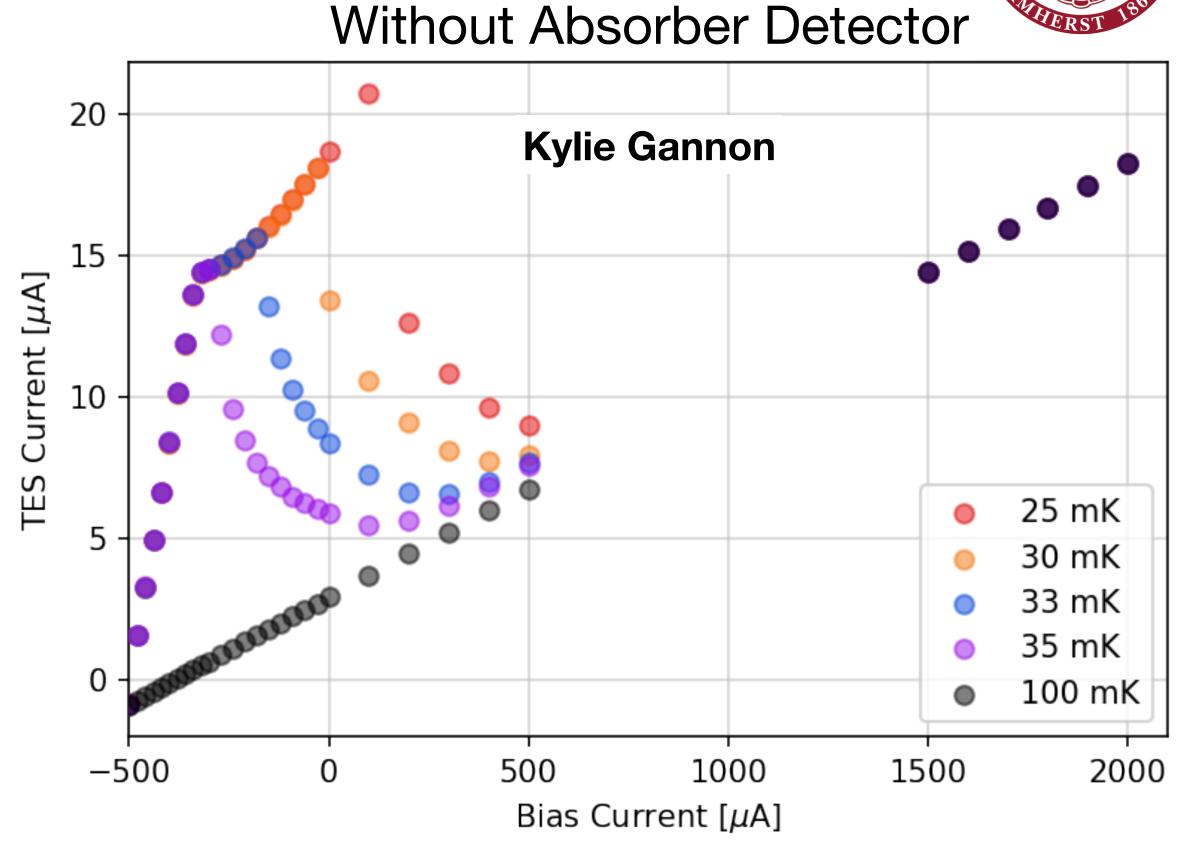
Thermal Conductances Received Scattering Program





- Measure IV curves at different temperatures to estimate power-vs-temperature
- Fit to find conductance and temperature scaling
- While these are within a factor of a few of expectation, lots of room to improve our understanding through modeling

$$P = K(T_c^n - T_b^n)$$



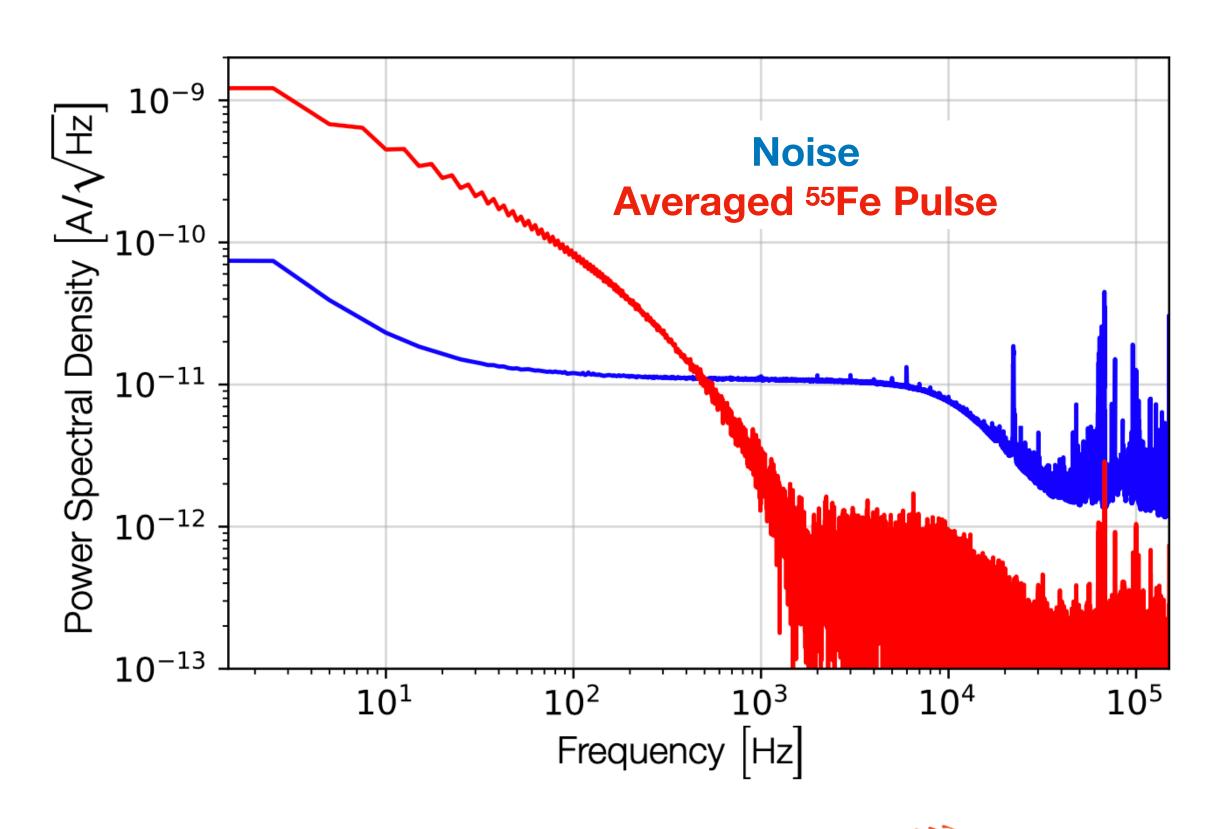
TES Channel	G at T_c [pW/K]	G at 20 mK $[pW/K]$
With Absorber	470 ± 200	470 ± 200
Without Absorber	1600 ± 400	390 ± 100

Data, Noise and Optimal Filtering



- Data continuously recorded at 300 kHz
- Triggering performed offline
- Energy estimation done through an optimal filtering framework
- Pulse shape taken to be an ⁵⁵Fe X-ray incident on the silicon target (with absorber detector)

$$\chi^2 = \int \frac{df}{J(f)} \left| \tilde{V}(f) - A \tilde{S}(f) \right|^2$$
 Noise Signal Template

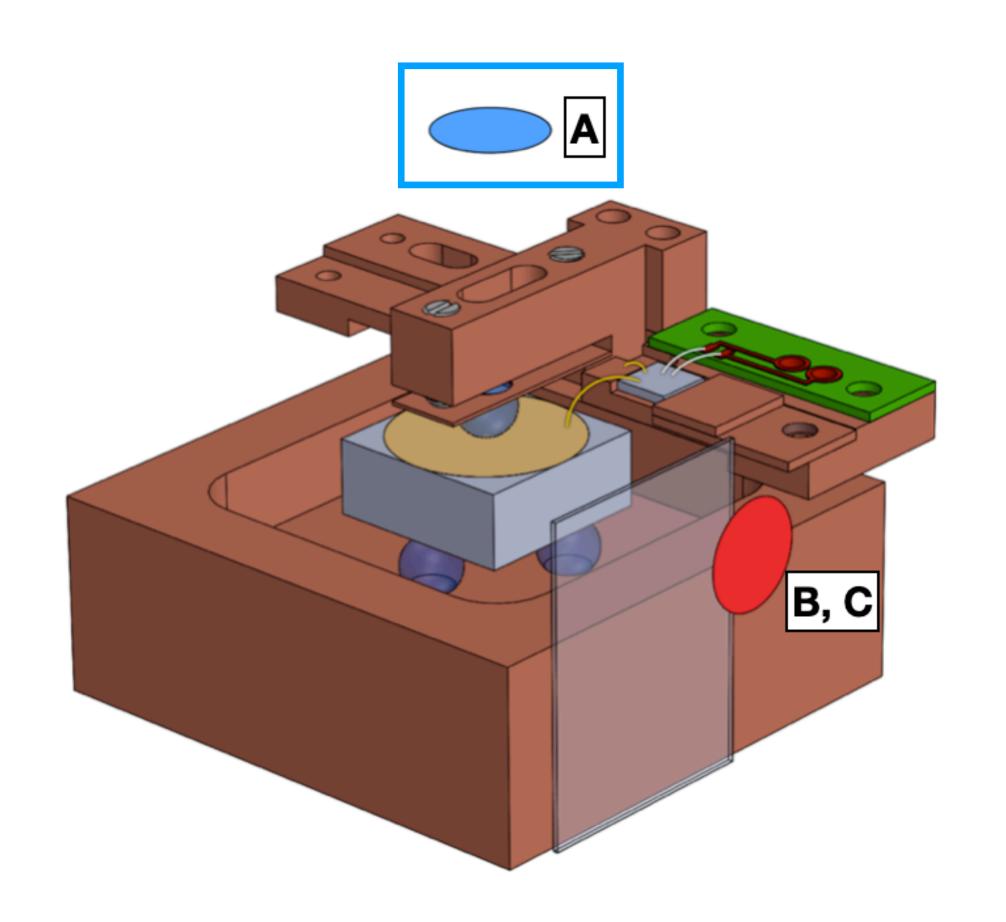




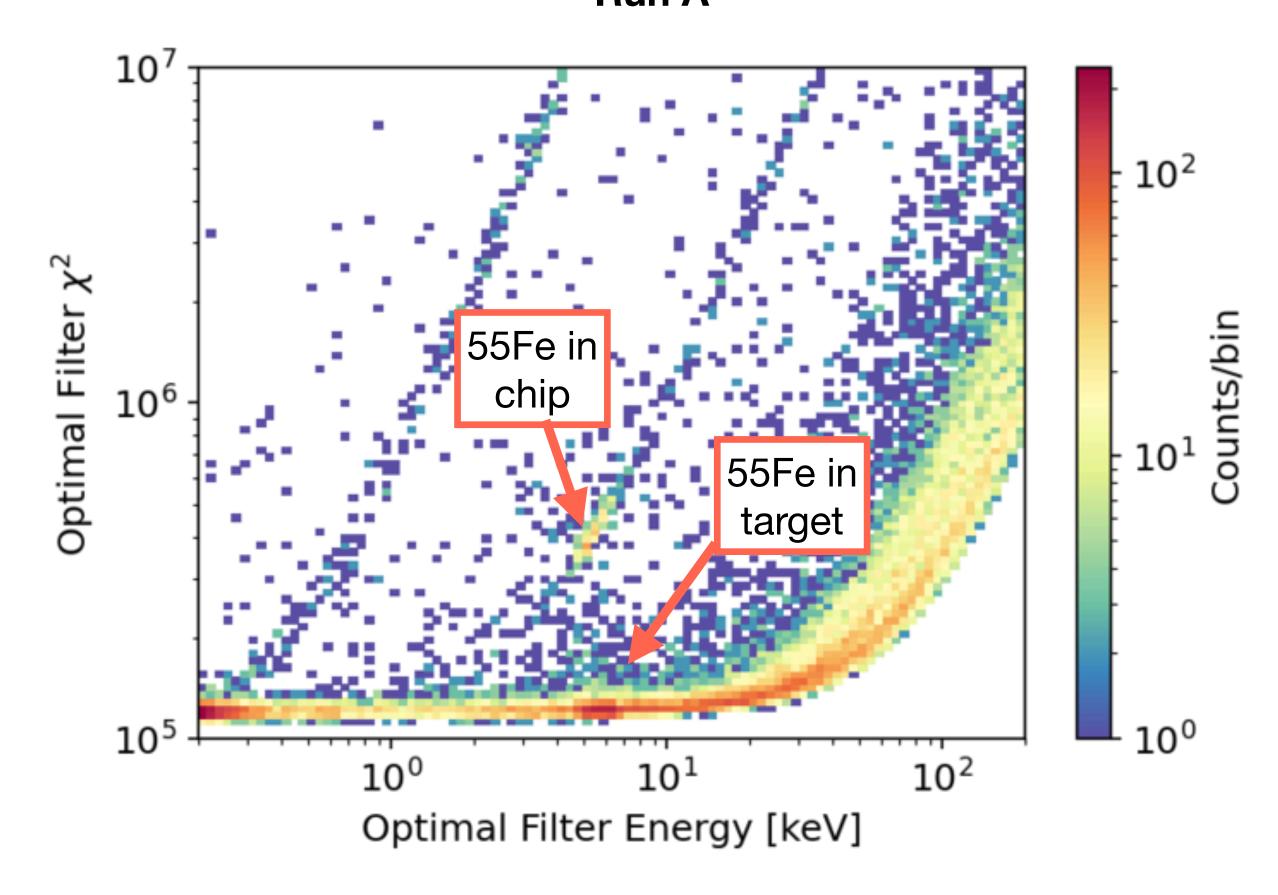
Optimal-Filtered Space Richerent Neutrino Scattering Program



See peaks from our X-ray source



With Absorber Detector Run A

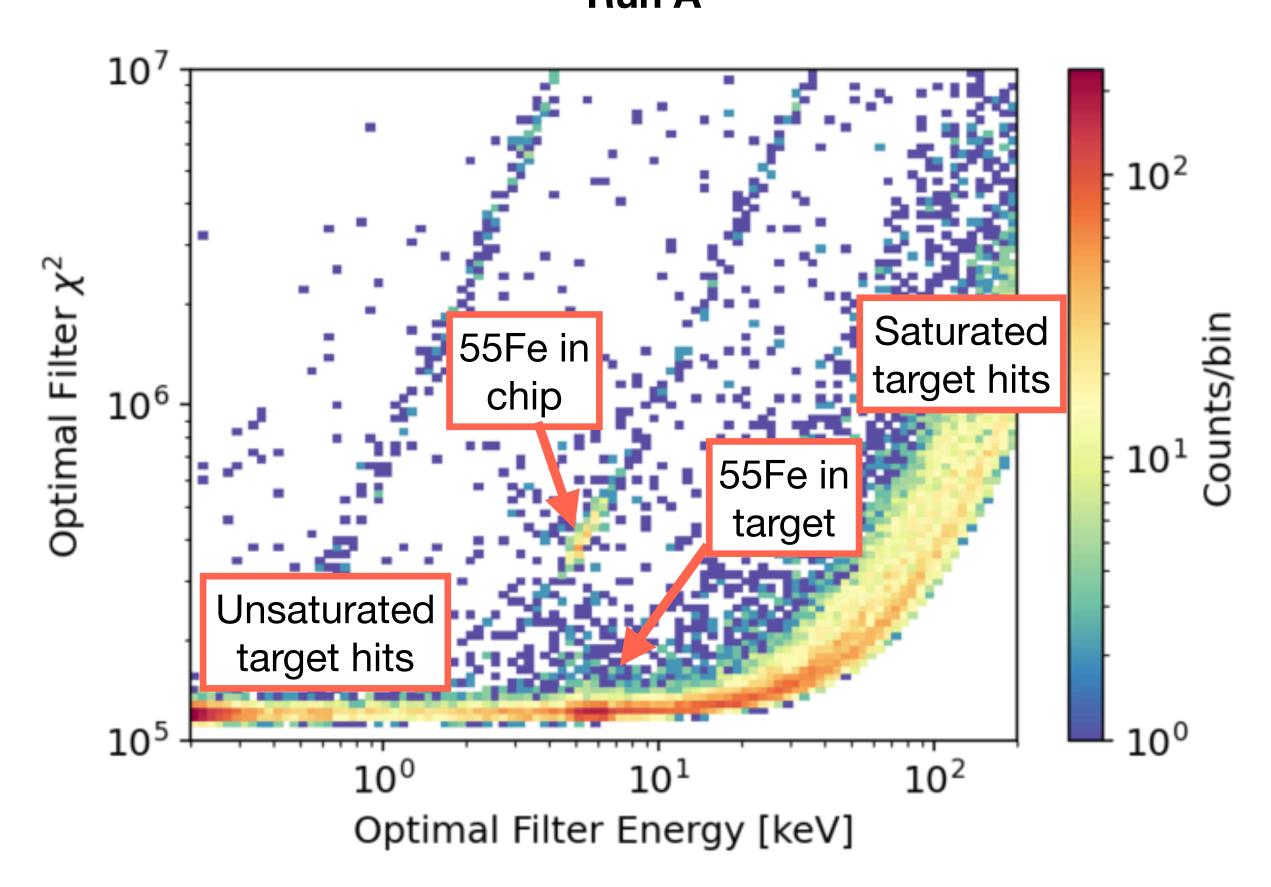


Optimal-Filtered Space Richerting Program



- See peaks from our X-ray source
- Three main branches in the data
- "Target hit" branch, events interacting in the Si

With Absorber Detector Run A

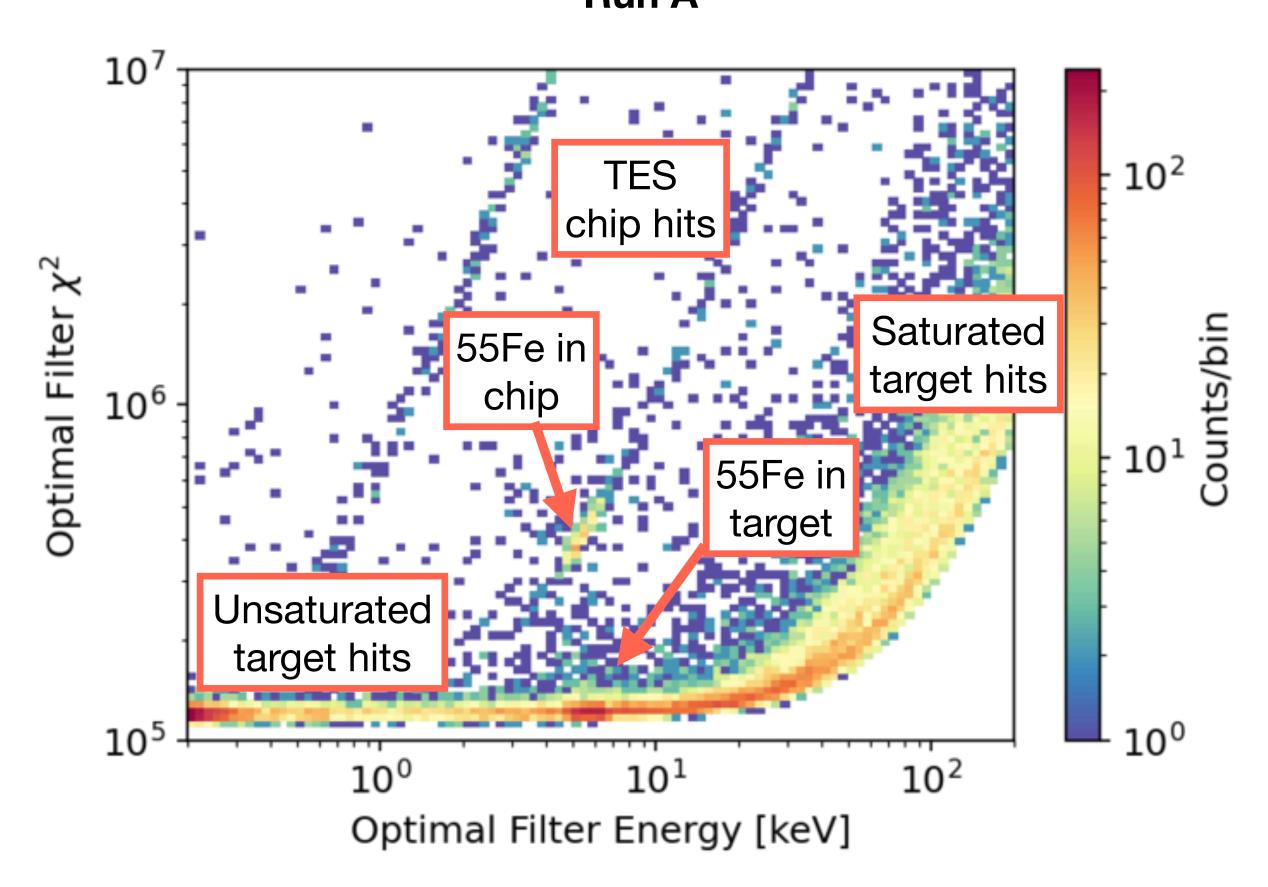


Optimal-Filtered Space Richering Program



- See peaks from our X-ray source
- Three main branches in the data
- "Target hit" branch, events interacting in the Si
- "Chip hit" branch of events hitting just the TES chip

With Absorber Detector Run A

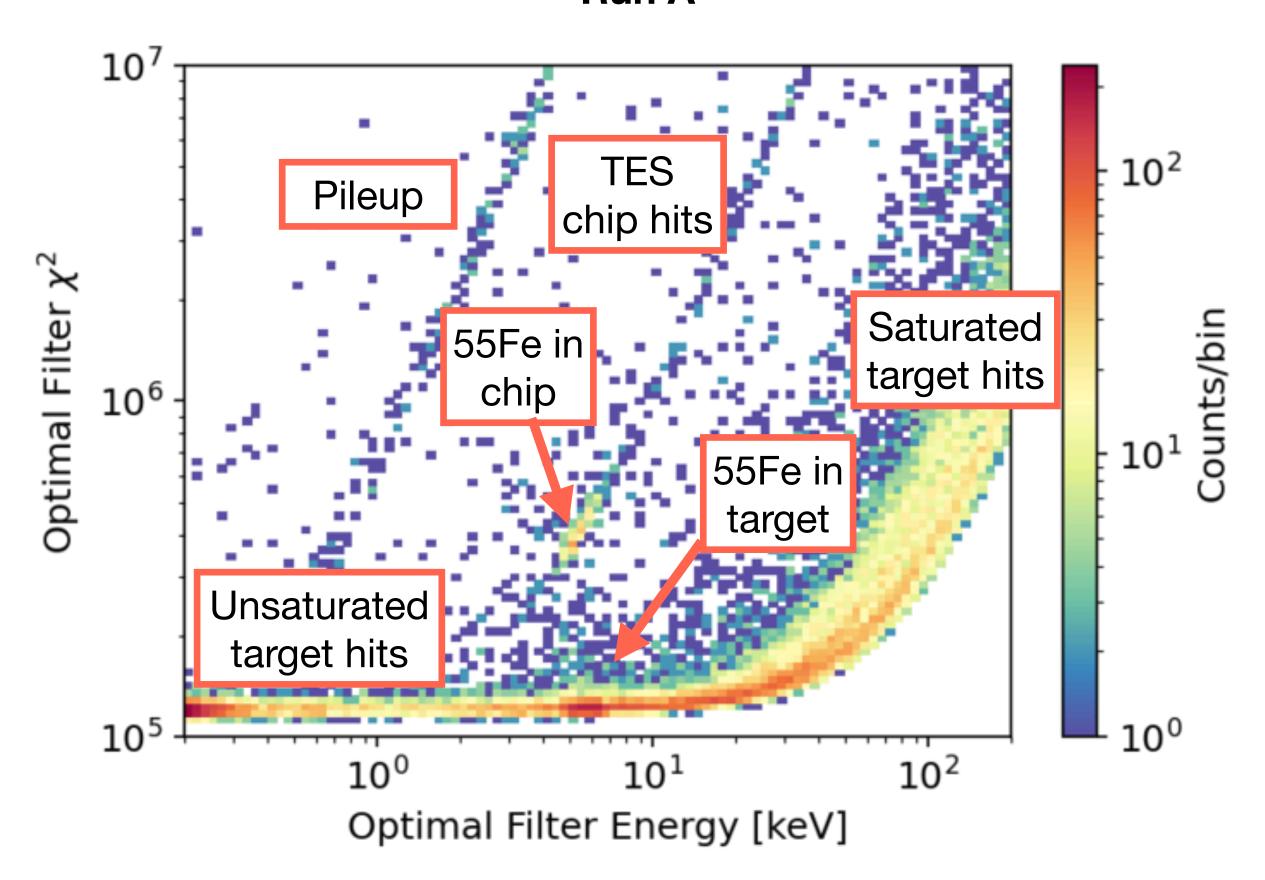


Optimal-Filtered Space Richard Scattering Program

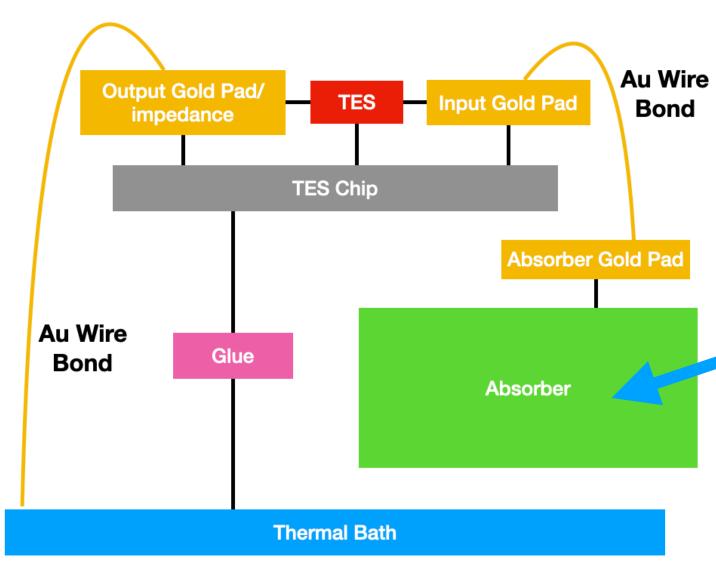


- See peaks from our X-ray source
- Three main branches in the data
- "Target hit" branch, events interacting in the Si
- "Chip hit" branch of events hitting just the TES chip
- "Pileup" events

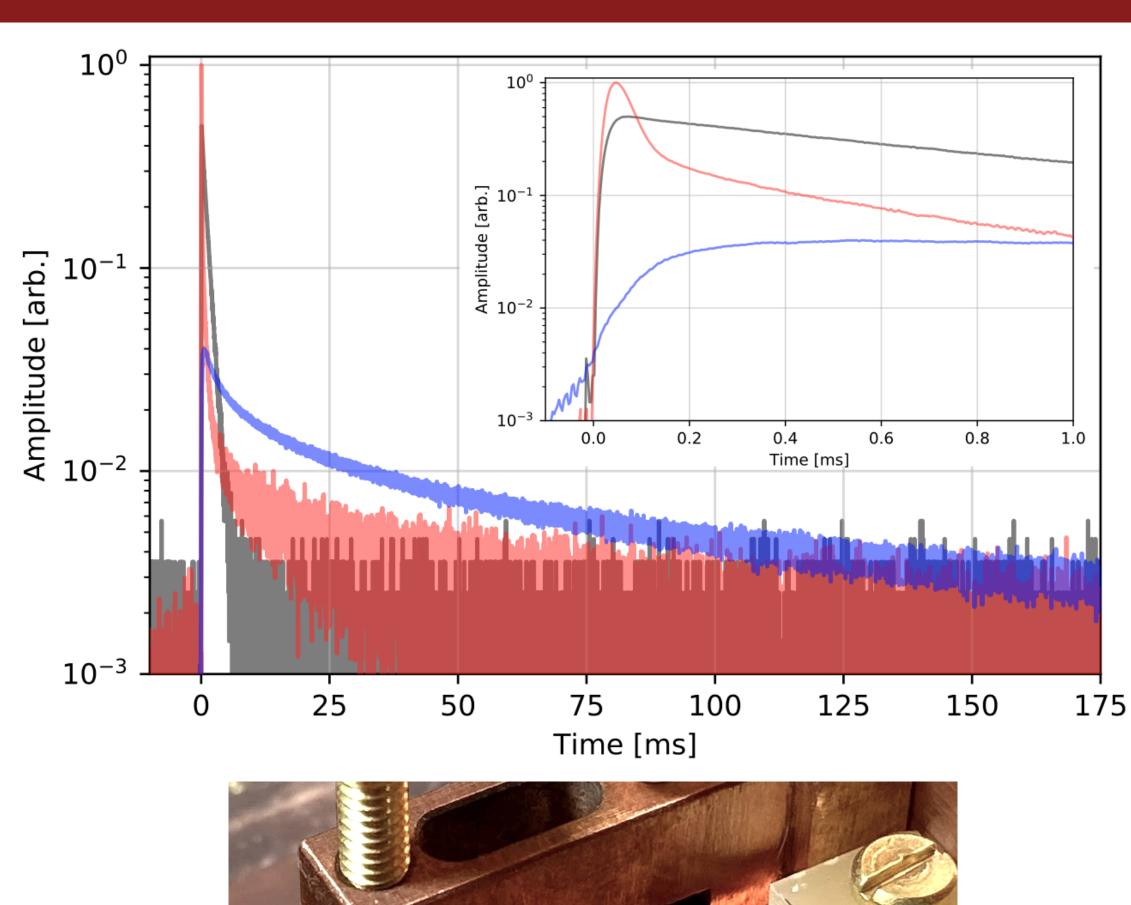
With Absorber Detector Run A

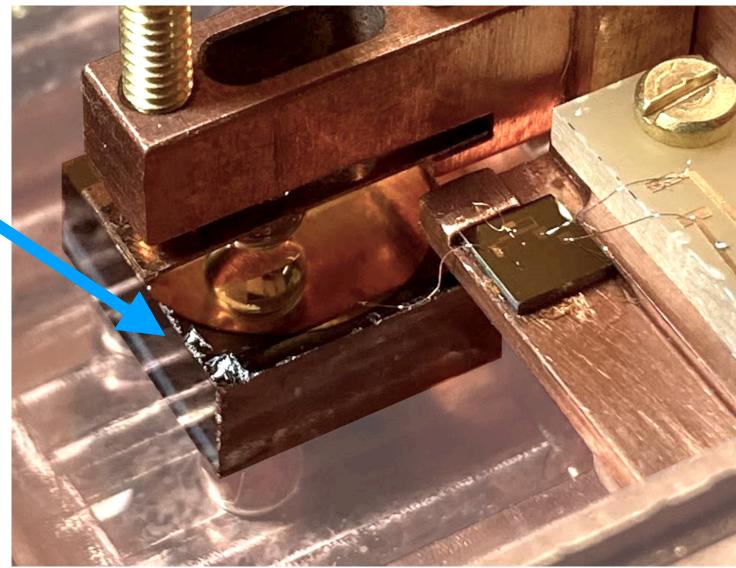


• Blue: Si target hit



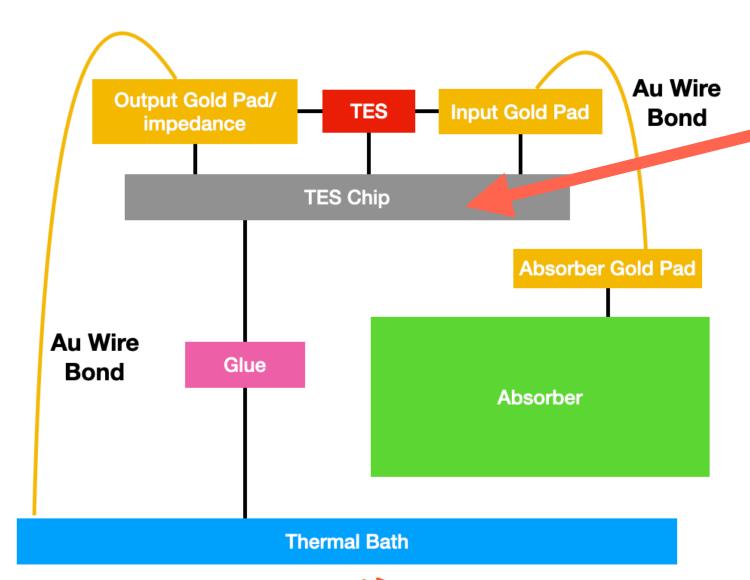




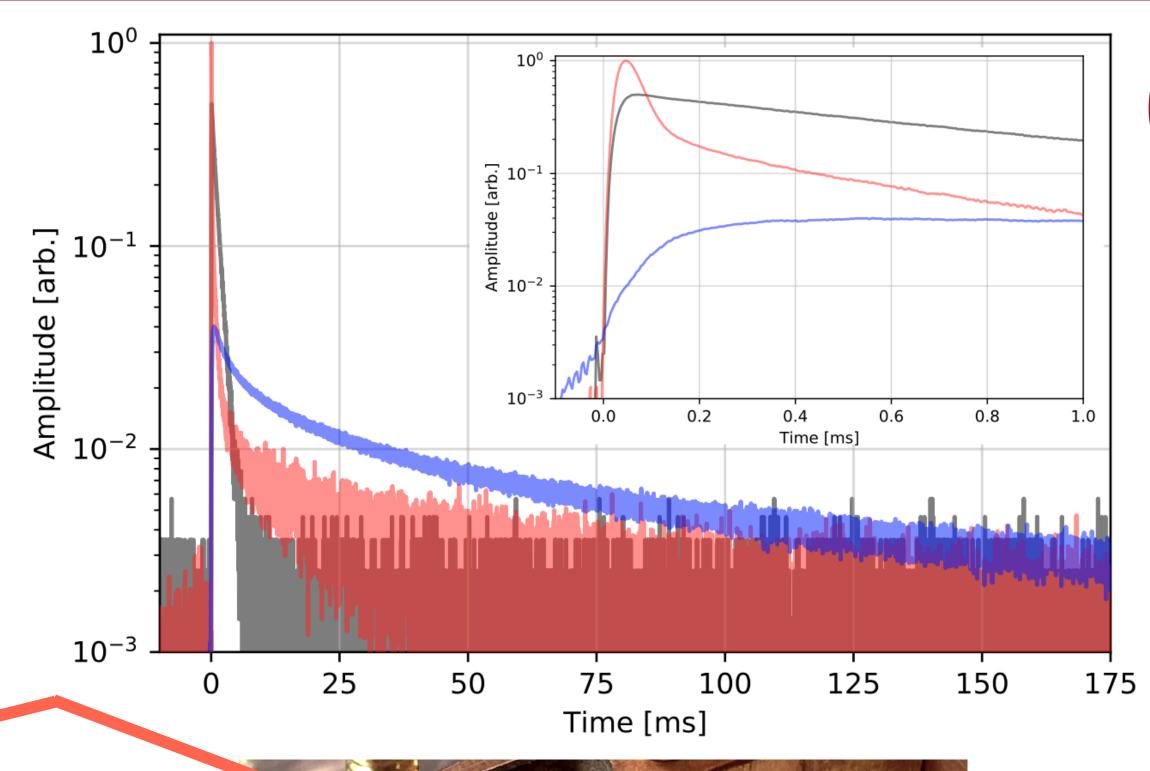


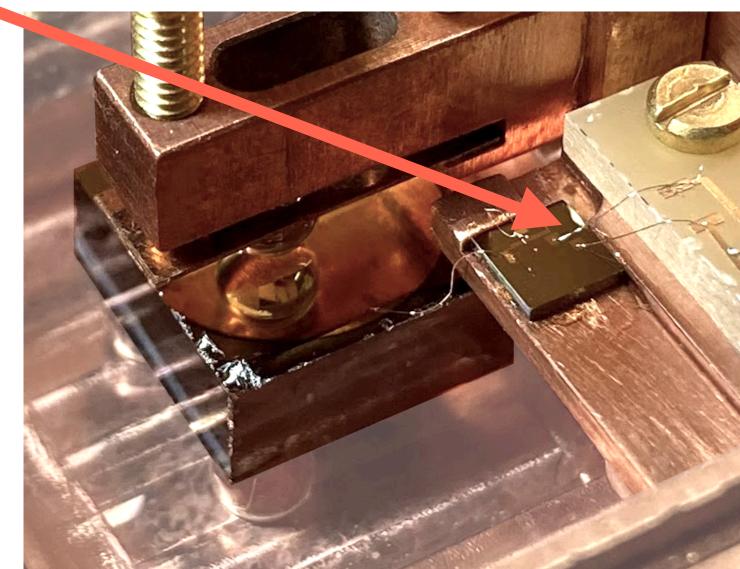
Blue: Si target hit

Red: TES chip hit





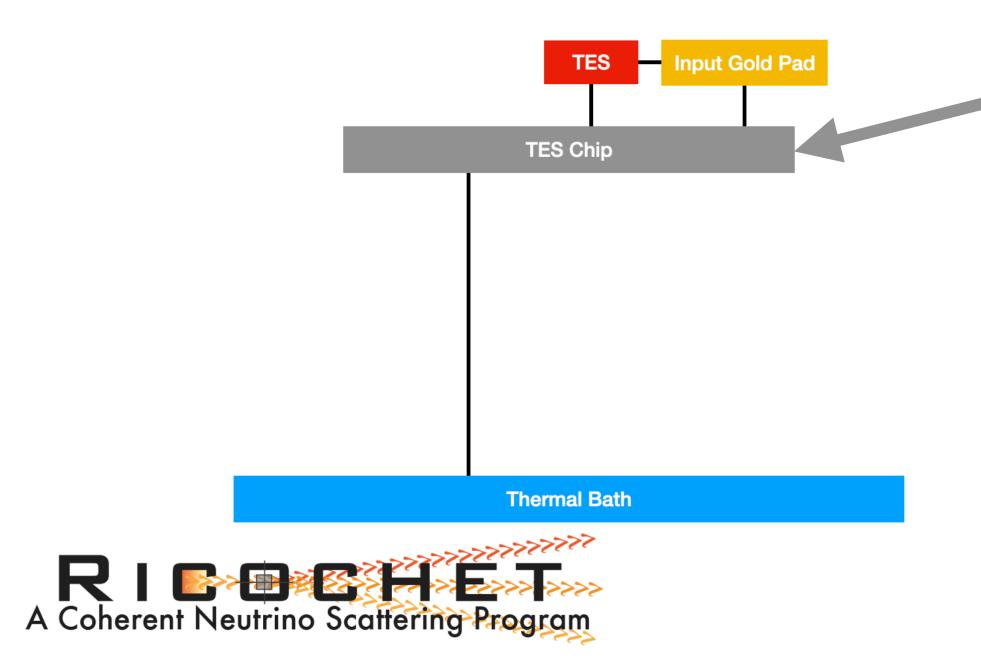


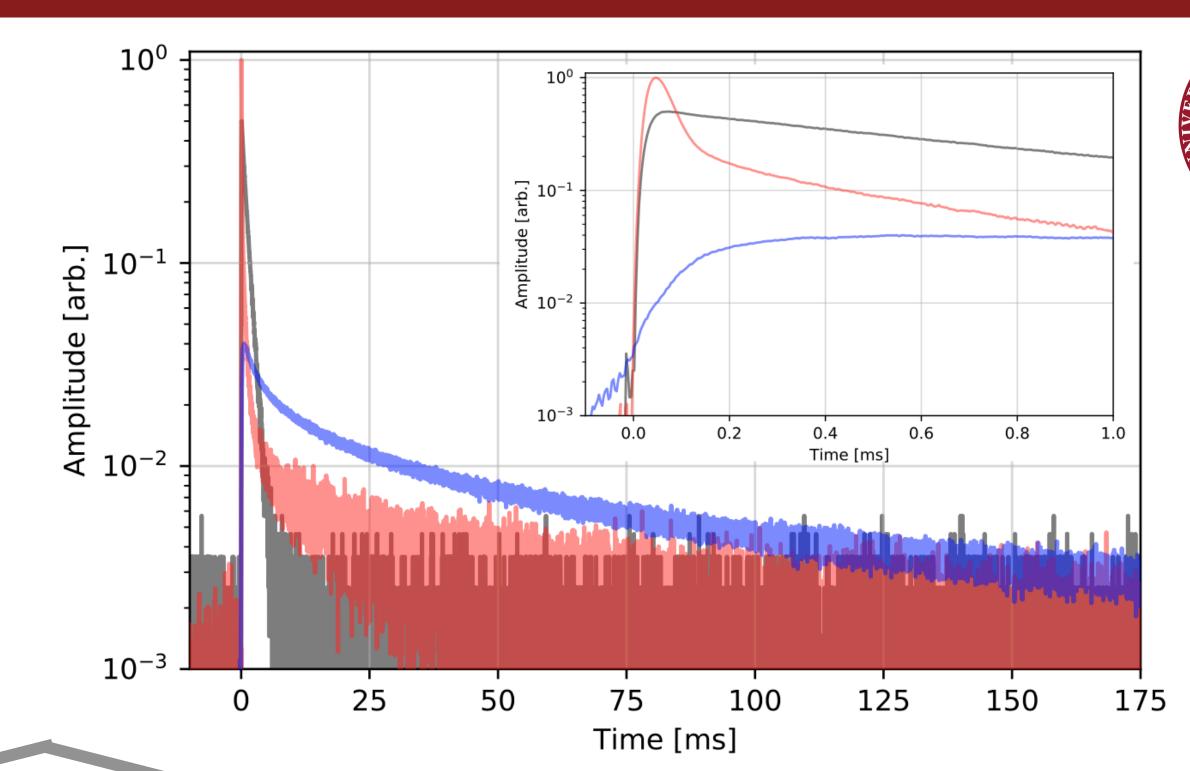


Blue: Si target hit

Red: TES chip hit

Black: Without absorber detector hit







Blue: Si target hit

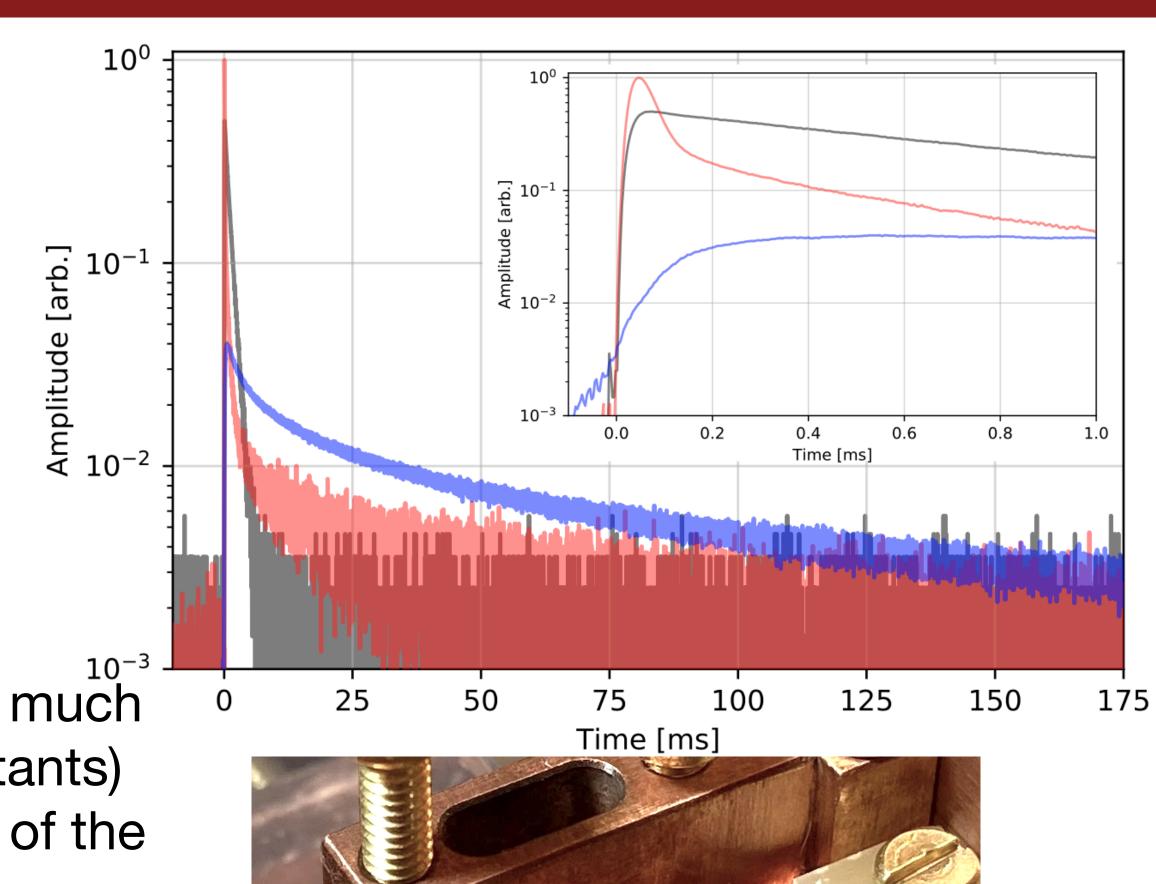
Red: TES chip hit

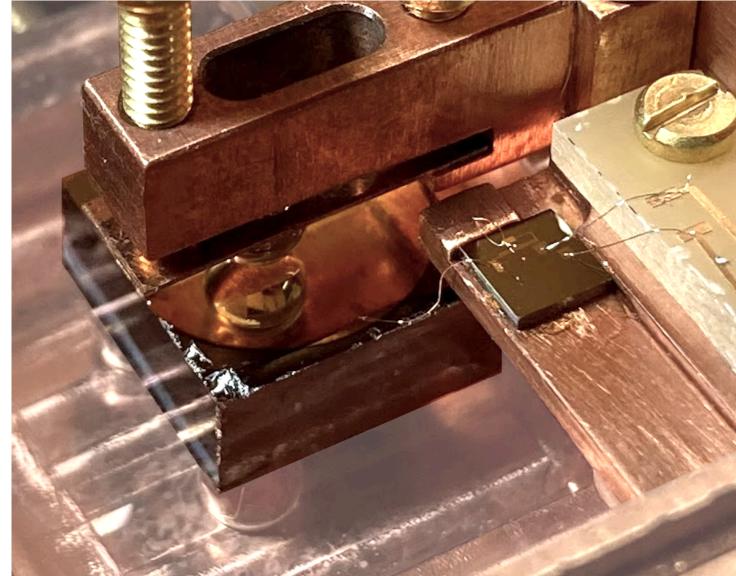
Black: Without absorber channel hit

 Events on the with absorber detector are much more complex (large variety of time constants) compared to the single fall time constant of the without absorber detector

 Again, lots of interesting modeling to do to understand these detectors







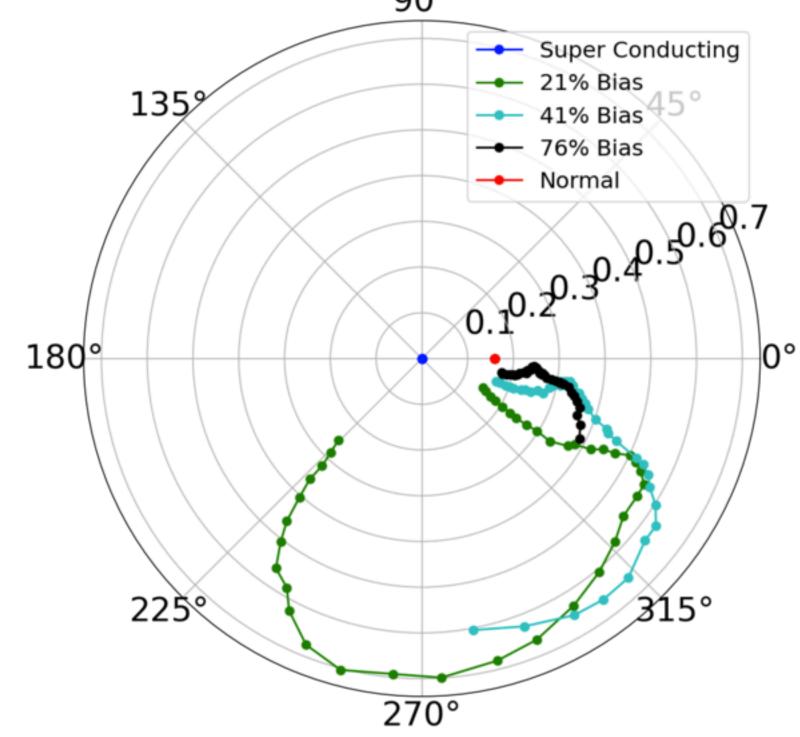
Next Steps: Modeling



- Compare in greater detail our data with the thermal model
- Includes the pulse data, as well as some initial complex impedance data
 - Collected at UMass Amherst (Charlie Veihmeyer) and Argonne National Lab (Ran Chen)
- More data with lower frequencies has been collected and is being analyzed

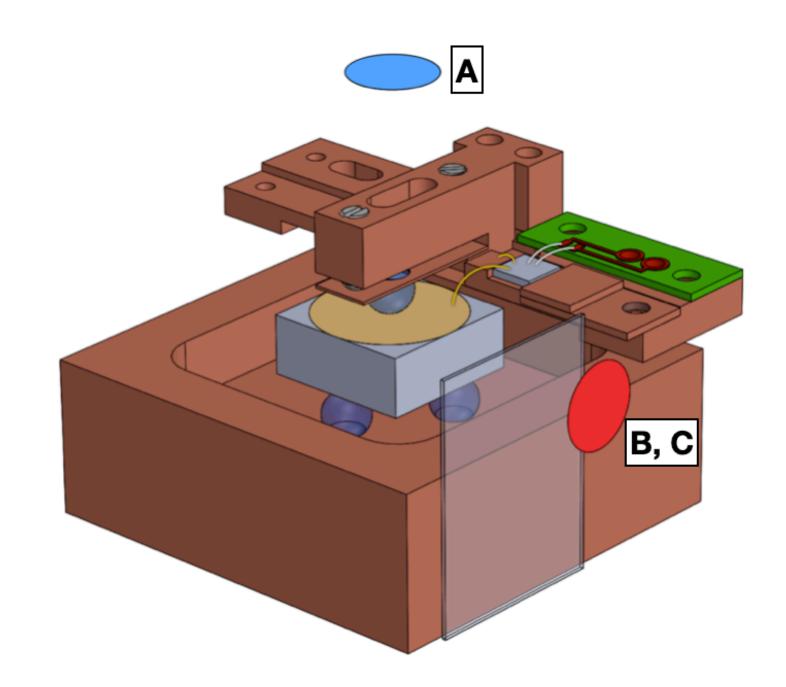
Charlie Veihmeyer

Polar Plots of Complex Impedance of TES Device 90°

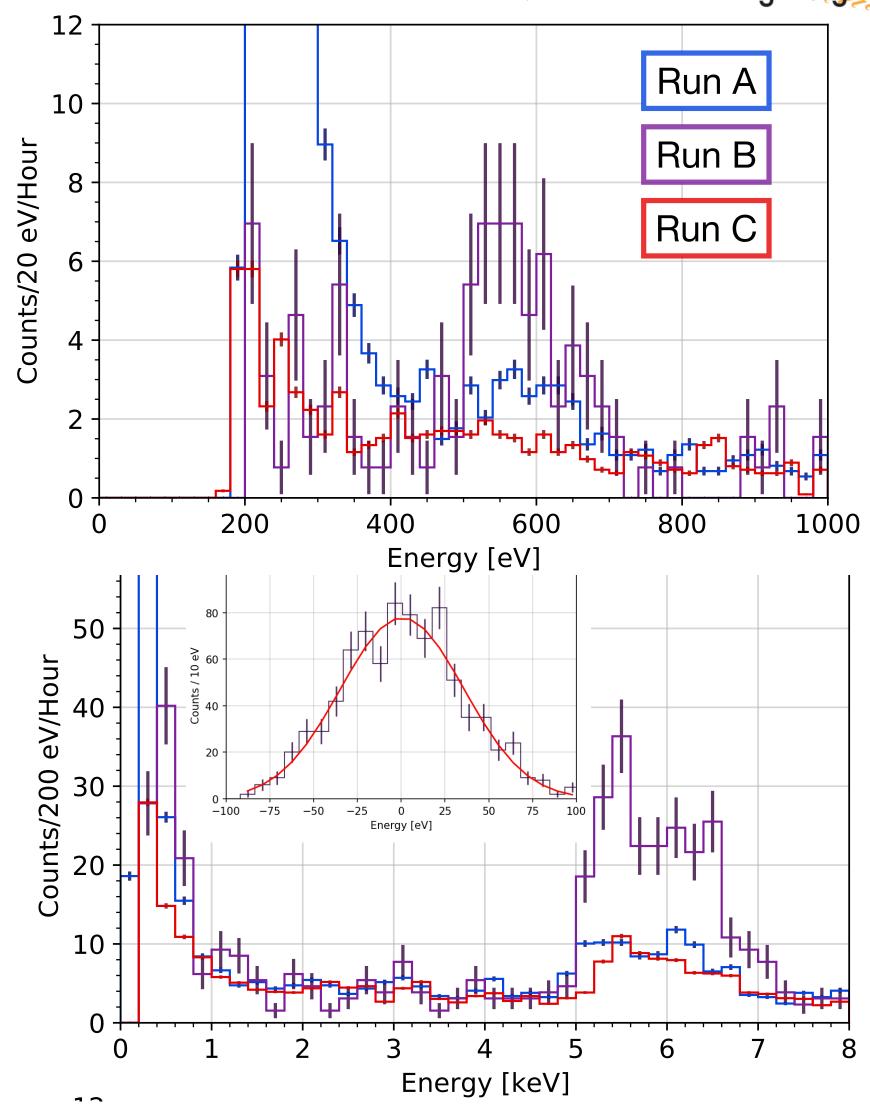


Spectra

- Energy resolution ~35 eV sigma baseline
- X-ray peak width significantly larger than this! (order ~1 keV)
 - Position dependence or some other effect?

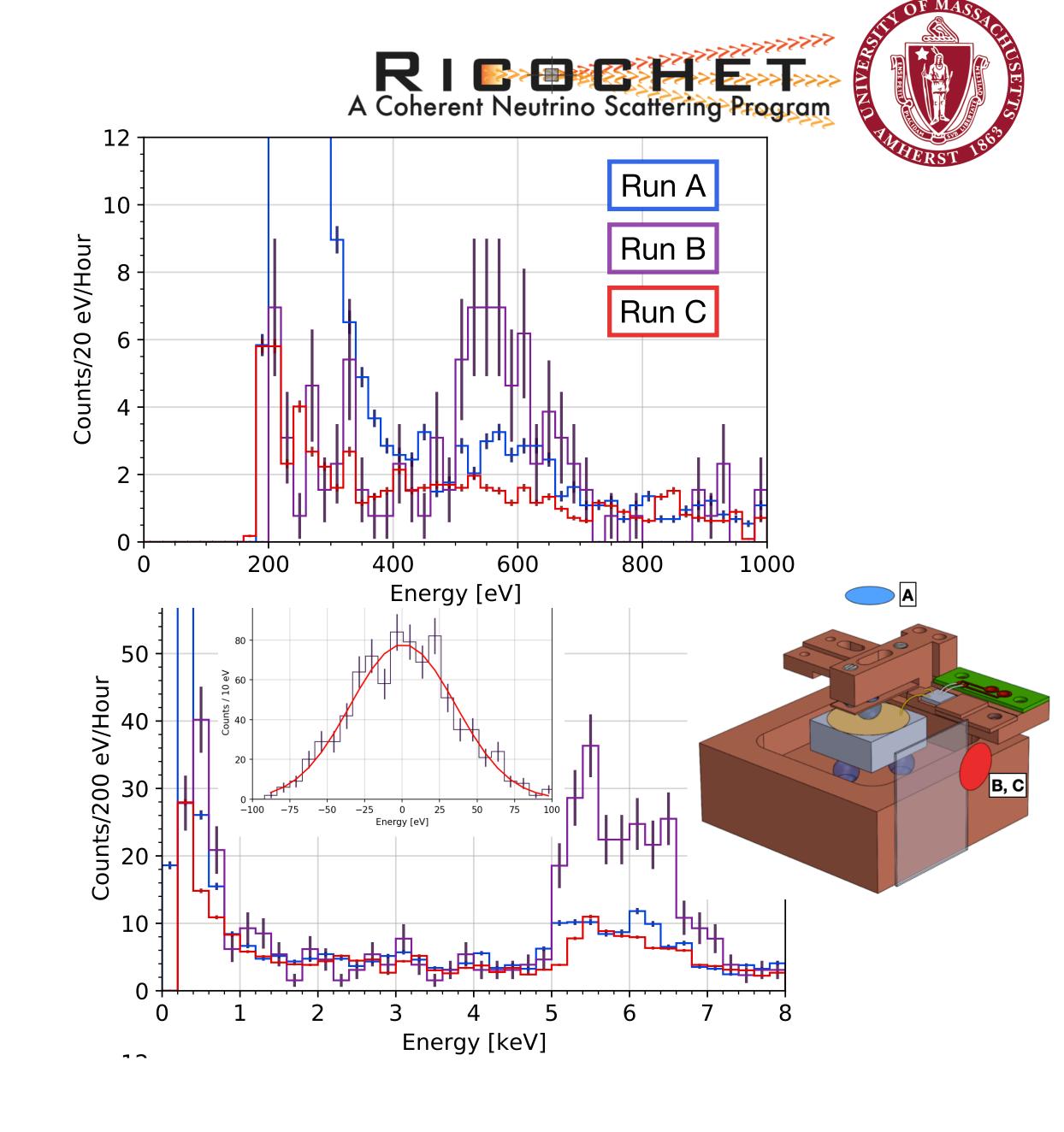






Spectra

- Energy resolution ~35 eV sigma baseline
- X-ray peak width significantly larger than this! (order ~1 keV)
 - Position dependence or some other effect?
- Peak at 550 eV? Disappears when blocking line of sight between X-ray source and sapphire ball
 - Sapphire scintillation? Heat conductance between sapphire and target?



Conclusions



- Several successful runs at UMass studying the modular TES design
- Many un-answered questions, modeling in particular

Paper with details coming to an arXiv near

you





Extras

Optimal-Filtered Space



- Three main branches in the data
- "Target hit" branch, events interacting in the Si
- "Chip hit" branch of events hitting just the TES chip
- "Pileup" events

